

SYNTHESIS AND CHARACTERIZATIONS OF ALUMINUM/GALLIUM CO-
DOPED ZINC-OXIDE NANOSTRUCTURES FOR HYDROGEN SENSORS

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ABSTRACT

Transparent electrode materials with the transparency of up to 80% in the visible wavelength region and resistivity as low as $10^{-3} \Omega\cdot\text{cm}$ are in high demand for various optoelectronic applications. It is believed that nanostructured Zinc oxide (ZnO) with modified electronic structure properties may be a promising alternative to Indium tin oxide (ITO). This is due to its similarity in band gap energy. This research attempted to improve the structural, morphological, optical and electrical properties of ZnO nanostructures by co-doping it with aluminium (Al) and gallium (Ga) (AGZO) in order to use the material as a hydrogen gas sensor. To achieve this goal, a series of Al/Ga co-doped ZnO nanostructure (NS) films with new morphologies was synthesised on the p-type Si (100) substrate using combined sol-gel and spin coating methods. Samples were annealed at different temperatures, time durations and laser energies to examine their effects on overall properties. The influence of varying Ga content was determined. FESEM images showed two new different morphologies for two different samples with increasing Ga content nanoleaves Ga (4 at. %) and nanopeanuts-like (5 at. %). The optical bandgap energy (3.26 - 3.20 eV) of AGZO nanofilms was discerned to be lower than pure ZnO films (3.37 eV). The resistivity of the prepared AGZO nanofilms at 1 at. % of Ga was found to be $4.571 \times 10^{-3} \Omega\cdot\text{cm}$ which was lower than Ga free (AZO) thin films ($6.4 \times 10^{-2} \Omega\cdot\text{cm}$). The sensing performance of the AGZO film was evaluated at (100 and 150) °C under varying H₂ gas concentrations (250 – 1750 ppm). The best sensitivity was achieved at a H₂ gas concentration of 1750 ppm. The improvement of overall properties was attributed to Ga mediated enhanced polycrystalline growth of the films and the production of new two different nanostructures. It was affirmed that the present method of sample preparation is simple and economical. The systematic characterisations might constitute a basis for producing high-quality ZnO nanofilms suitable for assorted applications. The laser annealing is a fast, cheap and better method than the thermal annealing method, but the annealing by the thermal method is the best to make a good hydrogen gas sensor in this study.

ABSTRAK

Bahan elektrod lutsiar dengan kelutsianran melebihi 80% dalam julat panjang gelombang nampak dan kerintangannya serendah $10^{-3} \Omega \cdot \text{cm}$ mempunyai permintaan yang tinggi bagi pelbagai aplikasi optoelektronik. Adalah dipercayai Zink oksida (ZnO) nanostruktur dengan sifat-sifat struktur elektronik yang diubahsuai mungkin merupakan salah satu alternatif yang baik kepada indium tin oksida (ITO). Ini adalah disebabkan tenaga jurang jalurnya yang hampir sepadan. Kajian ini bertujuan untuk meningkatkan lagi sifat-sifat ZnO nanostruktur darisegi struktur, morfologi, optik dan elektrik melalui dop ber sama dengan alumium (Al) dan gallium (Ga) (AGZO), membolehkan bahan tersebut digunakan sebagai sensor gas hidrogen. Untuk mencapai matlamat ini, satu siri filem Al/Ga co-dop pada filem ZnO nanostruktur (NS) dengan morfologi baru disintesis pada substrat jenis p Si (100) menggunakan kaedah salutan gabungan larutan gel dan putaran. Sampel telah disepuhlandap pada suhu, tempoh masa dan tenaga laser yang berbeza-beza untuk mengkaji kesan sifat-sifat keseluruhan terhadapnya. Pengaruh kandungan Ga yang berbeza-beza terhadapnya telah ditentukan. Imej FESEM menunjukkan, dua morfologi yang berbeza untuk dua sample berlainan dengan peningkatan Ga mengandungi "nanoleaves" Ga (4 at.%) dan "nanopeanuts-like" (5 at.%). Tenaga jurang jalur optik nanofilem AGZO (3.26 - 3.20 eV) didapati lebih rendah daripada filem ZnO tulen (3.37 eV). Kerintangan nanofilem AGZO yang disediakan pada 1 at.% daripada Ga didapati pada $4.571 \times 10^{-3} \Omega \cdot \text{cm}$ lebih rendah daripada filem tipis bebas Ga (AZO) ($6.4 \times 10^{-2} \Omega \cdot \text{cm}$). Prestasi penderia filem AGZO dinilai pada 100 °C dan 150 °C di bawah kepekatan gas H₂ yang berbeza-beza (250 - 1750 ppm). Kepekaan terbaik dicapai pada kepekatan gas H₂ 1750 ppm. Peningkatan sifat-sifat keseluruhan adalah disebabkan oleh pengantara Ga yang meningkatkan pertumbuhan polikristal bagi filem-filem tersebut dan pengeluaran dua nanosturuktur yang berbeza. Ini mengesahkan bahawa kaedah penyediaan sampel yang sekarang ini adalah mudah dan menjimatkan. Pencirian-pencirian yang sistematik mungkin membentuk asas untuk menghasilkan nanofilem ZnO yang berkualiti tinggi sesuai untuk pelbagai aplikasi. Penyepuh laser adalah kaedah yang cepat, murah dan lebih baik daripada kaedah penyepuh haba, tetapi penyepuhlandapan dengan kaedah termal adalah yang terbaik bagi menghasilkan sensor gas hidrogen pada kajian ini.

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LIST OF ABBREVIATIONS

0D	- Zero Dimension
1D	- One Dimension
2D	- Two Dimensions
3D	- Three Dimensions
AFM	- Atomic Force Microscopy
AGZO	- Aluminum Gallium co-doped Zinc Oxide
CB	- Conduction Band
COP	- cyclo-olefin polymer
CVD	- Chemical Vapor Deposition
DW	- Distilled Water
EDX	- Energy Dispersive X-ray Diffraction
FESEM	- Field Emission Scanning Electron Microscopy
FQ	- Fused Quartz
FT-IR	- Fourier Transform-Infra Red
FTO	- Fluorine-Doped Tin Oxide Coated glass
h	- Hour
HRTEM	- High Resolution Transmission Electron Microscopy
IR	- Infrared
ITO	- Indium Tin Oxide
JCPDS	- Joint Committee of Powder Diffraction Standards
MBE	- Molecular Beam Epitaxy
MOCVD	- Metal Organic Chemical Vapor Deposition
NBE	- Near Band Edge Emission
NBs	- Nanobelts
Nd:YAG	- Neodymium-Doped Yttrium Aluminum Garnet
NFLs	- Nanoflakes
NFs	- Nanoflowers
NFs	Nanoflowers
NIR	- Near Infrared
NLs	- Nanoleafs
Nm	- Nanometer

NPNs	- Nanopeanuts
NPs	- Nanoparticles
NRs	- Nanorods
NSs	- Nanosturctures
NWs	- Nanowires
PL	- Photoluminescence
PLD	- Pulsed Laser Deposition
PVD	- Physical Vapor Deposition
p-ZnO	- Pure ZnO
QCEs	- Quantum Confinement Effects
QDs	- Quantum Dots
RF	- Radio Frequency
RF	- Radio Frequency
RT	- Room Temperature
SEM	- Scanning Electron Microscopy
SEM	- Scanning Electron Microscopy
TEM	- Transmission Electron Microscopy
UV	- Ultraviolet
UV	- Ultraviolet
VB	- Valance Band
Vis	- Visible
V _{zn}	- Zinc Vacancies
XPS	- X-ray photoelectron spectroscopy
XRD	- X-ray Diffraction
Z _{ni}	- Zinc Interstitials
ZnO	- Zinc Oxide
Z _{no}	- Zinc Antisites
ZNPs	- Zinc Oxide Nanoparticles
ZNSs	- Zinc Oxide Nanostructures
ZAD	- Zinc acetate dehydrate
MEA	- Monoethanolamine
IPA	- Isopropanol

LIST OF SYMBOLS

I	-	Current
V	-	Voltage
α	-	thermal diffusivity
λ	-	Wavelength
μ	-	electron mobility
ρ	-	Resistivity
D	-	grain size
V	-	volume
δ	-	dislocation density
Θ	-	diffraction angle
β	-	Full Width Half Maximum
ϵ	-	Strain
Tc	-	texture coefficient
σ	-	Stress
L	-	bond length
μ_H	-	Hall mobility
μ	-	Mobility
R	-	Resistance
ρ	-	Density
n_e	-	electron concentration
hkl	-	Miller indices
d_{hkl}	-	inter planer distance
a,c	-	lattice parameters
E_g	-	energy gap
X_c	-	the fraction of crystalline phase
E_L	-	laser energy
S	-	sensitivity
M	-	molecular weight
O _v	-	Oxygen Vacancies
O _i	-	Oxygen Interstitials
O _{Zn}	-	Oxygen Antisites
n-type	-	Donor type

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CHAPTER 1

INTRODUCTION

1.1 Background of the Study

At present, the sophisticated tools needed for functional materials designs, characterisations, synthesis, and applications encompass the manipulation of diverse materials in the range of 1 to 100 nm (nanoscale). Distinctive facets including indirect, direct and conceptual aspects are exploited for the evolution of nanoscience and nanotechnology (Shastri et al., 2010). The indirect aspect of nanotechnology refers to the advancement in the miniaturisation of existing technologies which open up new avenues of applications. In addition to indirect, direct signifies the appliance of new nanoscale objects to develop a novel process, material, mechanism and performance for completely exotic purposes. Lastly, the conceptual aspect of nanotechnology encompasses all nanomaterials and processing technologies at the molecular or atomic level particularly involving the living organism and bio-system. For instance, information and communication technology (ICT) benefitted tremendously from emerging nanotechnology concepts where novel semiconductor and optoelectronic materials were synthesised to achieve new nanodevices (Michael et al., 2008).

Nanotechnology has penetrated every field of science and technology including the environmental sciences (filtration), the energy sectors (for energy cut, tackle increased energy consumption, efficient production of energy, cleaning up nuclear accidents and storing and recycling of wastes), heavy industries (aerospace engineering and chemicals), consumer products, bio-medicine, food technology, forensics, and defence. In the past few decades, rapid progress in nanomaterials synthesis and characterisations has opened up several new avenues of nanotechnology. Many advanced functional materials with unusual properties have been developed (Poole et al., 2003).

In the area of wide bandgap semiconductor materials, ZnO thin films have extensively been used in many applications including piezoelectric transducers, windows in solar panels, gas sensing, devices for the detection of surface acoustic waves, optical waveguides, acousto-optic devices, transparent conductive electrodes and varistors (Look, 2001). ZnO is a unique semiconductor because of its broad bandgap (~3.37 eV) and high exciton binding energy of 60 meV (Triboulet et al., 2003). Furthermore, it is a potential candidate for blue and ultraviolet (UV) light-emitting diodes and laser diodes, backlight diodes for liquid crystal display (LCD), mobile phones and automotive lighting. Nowadays, it is intensively used in optoelectronic devices because of its strong excitonic absorption and recombination at room temperature (Yamamoto et al., 2001).

The existence of excess conduction electrons in ZnO nanostructure leads to an enhanced electrical conductivity. This is useful in transparent conductive electrodes as a substitute to indium tin oxide, commonly referred to as ITO. The primary sources of these excess electrons are defects (Kohan et al., 2000), which can be intrinsic or extrinsic impurity defects. Extrinsic defects are recognized as dopants when deliberately introduced to a system to enhance various properties (Maller, 2016). Three types of defects are present in the ZnO crystal: vacancies, interstitial atoms and antisites of oxygen and zinc (Flemban, 2017).

Zinc oxide is a natural wurtzite structure which is an n-type semiconductor due to intrinsic defects such as O vacancies (V_O) and Zn interstitials (Zn_i). Al acts as a donor on a lattice site [Al_{Zn}] and an acceptor on an interstitial site [Al_{Zn_i}]. Al atoms are substituted into the structure due to the fact that the Al^{3+} radius (0.054nm) and Zn^{2+} radius (0.074nm) are similar. Thus, Al^{3+} ions easily substitute for Zn^{2+} . Zinc has two valence electrons and aluminium has three valence electrons.

It is confirmed that the concentration of oxygen vacancies and Zn interstitials are the most abundant native defects and can be changed with the Zn partial pressure. The results of an electron concentration displayed that with a high partial pressure of Zn, electrons dominate the content of the hole (Kohan et al. 2000). Thus, intrinsic ZnO donors do not significantly participate in the electrical conduction in ZnO. Elements in-group III (Al, Ga and In) with valence cell configuration of $ns_2 np_1$ possess lower

ionisation energy compared with Zn (ns_2). Thus, such elements can substitute Zn^{2+} ions in the lattice site of ZnO crystal. Donation of excess electrons increases the carrier concentrations to a value greater than 10^{20} cm^{-3} , resulting in an enhancement in electrical conductivity (Yamamoto et al., 2001).

To synthesise ZnO nanoparticles, many researchers have used physical methods such as radio frequency (RF) sputtering (Uikey et al., 2016) and molecular beam epitaxy (MBE) (Maller, 2016). However, structural inhomogeneity and cost remain disadvantageous for large-scale synthesis by physical means (Diaz De Leon et al., 2017). On the other hand, many researchers have synthesised ZnO nanoparticles using chemical methods such as chemical bath deposition (Flemban, 2017), hydrothermal synthesis (Wei et al., 2013) and the sol-gel method (Maache et al., 2017). Amongst these techniques, sol-gel is the preferred for the preparation of thin film owing to its low cost, outstanding control on the precursor solution stoichiometry, simple modifications of compositions, homogeneity, low temperature and non-requirement of a vacuum (Vajargah et al., 2013). Moreover, sol-gel deposited ZnO thin film samples reveal a high performance and a smaller number of defects which are beneficial for many applications. Several authors have reported the impact of sol-gel on controlling ZnO nanoparticle's shape and size (Diaz De Leon et al., 2017). Compared to other chemical methods in terms of reaction mechanisms such as hydrolysis and condensation, the sol-gel method offers highly uniform dispersion of dopants in the ZnO crystal lattice. Some researchers have used the sol-gel method with polymerising agents such as starch, nitric acid and dextrose to control the nanoparticles' shape and size (Diaz De Leon et al., 2017). Moreover, wide bandgap materials are chemically and thermally more stable, which is an advantage for devices operating in harsh environments (Liu et al., 2010). Among these materials is ZnO which has been studied extensively in recent years for its unique properties and potential application in electronic and optoelectronic devices (Liu et al., 2010). It has strong radiation hardness, high chemical stability, low cost and a large bandgap of 3.37 eV at room temperature (Liu et al., 2010).

Hydrogen is a non-toxic, non-poisonous, colourless, odourless and tasteless gas that cannot be detected by human senses. Hydrogen has a very low density (0.0899

kg/m³) with a high diffusion coefficient in the air (0.61 cm²/s). The H₂ content in the air at sea level is 0.5 ppm and has no threshold limit value (Schwandt & Fary 2000). Hydrogen can be ignited easily with a very small amount of energy, as low as 0.02 mJ (Hübert et al. 2011) and the explosive range is wide, from 4% to 75% (Al-Hardan et al. 2010). The monitoring of hydrogen concentration is essential to nuclear reactor safety (Hübert et al. 2011). In coal mines, hydrogen can be produced in the ppm² range by methane or coal-dust explosions or by the spontaneous heating and low-temperature oxidation of coal (Brungs et al. 1992).

Hydrogen is an energy carrier and can contribute to overcoming problems of dwindling fossil fuel reserves, energy supply security and climate change (Hübert et al. 2011). In 2006, 10,638 thousand tons of H₂ was produced in the United States. Most of this H₂ was used in petrochemical plants, fertiliser plants (ammonia production) and the methanol industry (Korotcenkov et al. 2009). A minuscule fraction of H₂ (50 tons in 2006) was used as an alternative fuel for electric power generation and transportation. This small fraction of H₂ used in power generation and transportation is growing rapidly, resulting in a greater presence and distribution of H₂ in society. In this emerging hydrogen economy, the detection of hydrogen leaks and the measurement of hydrogen concentration are necessary during production, storage, transportation and use in both stationary and mobile applications (Hübert et al. 2011). Sensors will, therefore, be used for safety monitoring of hydrogen production plants, pipelines, storage tanks, refuelling stations and automotive vehicles (Hübert et al. 2011).

Alternative hydrogen detection methods employ instruments such as gas chromatographs, mass spectrometers or specific ionisation gas pressure sensors. Traditionally, these instruments are large, expensive, high maintenance and slow in terms of their sampling and reaction times (Hübert et al. 2011). Therefore, it has become a priority in research to investigate various techniques to develop a H₂ sensor with a high sensitivity and a fast response time. Hydrogen sensors have several advantages over the conventional hydrogen detection methods, including their lower cost, smaller size, and faster response. These advantages make them more suitable for portable and in situ hydrogen detection in a range of applications (Hübert et al. 2011).

Commercially available sensors are primarily based on semiconductor metal oxides, electrochemical H₂ oxidation, catalytic response, thermal conductivity response or optical response technology. Although these sensors are sensitive and reliable, electrochemical based sensors particularly suffer from a decrease in sensitivity with time due to deterioration of the electrode catalyst. Catalyst based sensors are not specific to H₂ and often need high temperatures or high power for their operation. The most successful commercial sensors based on metal oxides are small in size, highly responsive, cheap and operate using a relatively simple electric circuit. However, these sensors require a significant pre-heating of the sensing element up to 300-700 °C to achieve the desired sensitivity and accuracy (Lupan et al. 2010). Recently, efforts in H₂ sensor development using metal oxides have focused on improving the sensitivity and decreasing the operating temperature. In-room temperature sensing ZnO has shown improved response and short recovery time due to its wide band-gap and surface adsorbed oxygen species. Furthermore, it is a cost-effective, easy, fast reproducible synthesis in nanostructured form.

Research has found that the resistivity of AGZO thin films ($2.14 \times 10^{-3} \Omega\text{-cm}$) is lower than AZO thin films ($6.40 \times 10^{-3} \Omega\text{-cm}$) (Lee et al. 2009). Furthermore, (Han et al. 2010) reported that depending on the Ga doping level, the grain size increases to reduce grain boundary scattering. In their study, the resistivity of AZO films decreased from 3.5×10^{-3} to $8.1 \times 10^{-4} \Omega\text{-cm}$ by Ga doping at 2.1 at.%. By Ga doping, the Hall mobility was improved, and the carrier concentration was increased. Ga acted as an intrinsic donor. Enhancing the conductivity of AZO nanostructures by Ga doping using sol-gel and spin coating which can synthesize two and three-dimensional nanostructure, the efficiency of devices can be enhanced. Thus, the synthesis of co-doped ZnO nanostructures using sol-gel and spin coating is reported.

1.2 Problem Statement

Nanostructured ZnO can be synthesised using a number of methods including vapour solid (VS), vapour-liquid-solid (VLS), radio frequency (RF) and sol-gel. VS and VLS require high temperatures for the growth of nanostructures. RF requires

expensive instruments and specialised laboratory setup. On the contrary, the sol-gel method is cost-effective and can synthesise ZnO with controlled nanostructure morphology and dopants. However, the sol-gel methods for the synthesis of a ZnO nanostructure on Si substrate are not well characterised.

One dimensional (1D) and two-dimensional (2D) ZnO nanostructures have a high surface to volume ratios, which make them valuable for a variety of applications (Ali et al., 2010). Although there are different methods used to fabricate 2D ZnO nanostructures, the sol-gel spin coating method is the easiest and is able to fabricate 2D ZnO nanostructures at low temperatures (Cheng, et al., 2009).

It has been found that the structural, electrical and optical properties of ZNS-based thin films can remarkably be improved by co-doping with Aluminium and Gallium (Al/Ga) but a few studies have explored this possibility thus far. Moreover, the capacity of combined sol-gel and spin-coating (a chemical approach) for the preparation of ZNSs-film co-doped with Al/Ga has not been reported in the literature, but they were used many (physical approaches). It is necessary to prepare high-density ZnO NSs-film co-doped with Al/Ga using a novel combined technique of laser annealing with different energies (Vajargah et al., 2013). This method needs to be implemented under different growth conditions to determine the influence of changing substrates type, annealing temperature and time, laser annealing energy and Al/Ga concentration ratio on the structures, morphologies, electrical as well as optical properties of ZnO NSs-film samples co-doped with Al/Ga. Growth optimization is a prerequisite to achieving optimum ZnO NSs-film co-doped with Al/Ga which is advantageous for high-performance gas sensing applications (Ivanova et al., 2015). The limitations associated with the existing synthesis techniques of Al/Ga co-doped ZNSs-film must be overcome by developing a simple, economical and eco-friendly sol-gel method. For diverse applications, high-density ZnO nanorods are required.

Moreover, in some cases, the sensor fabrication step requires the addition of various dopants which are very complicated and time consuming. The mono-doped (single element doping) system including Al:ZnO and Ga:ZnO thin films have some issues related to their stability, mechanical strength, efficiency morphology and hall

mobility that are disadvantageous for applications. By co-doping ZnO with more than one of the group III metallic elements these issues can be resolved (Bu, 2016). In addition to this, the expensive nature of Ga limits the mass production of Ga doped ZnO nanofilm. The impact of substrate type (Si) and changing laser annealing energy on the surface morphology of ZnO thin film grown by sol-gel route remains unresolved.

Researchers have used Al as a substrate to form the porous structure of ZnO nanoplates. Using Al as a substrate has some potential problems: (i) Al is quickly oxidised by atmospheric oxygen, (ii) Al is a good conductor and therefore a thick layer of Al under the ZnO nanostructure might be problematic in its application in electrical devices. The substrate used is p-type (Si) and changing laser annealing energy on the surface morphology of ZnO thin film grown by the sol-gel route remains unresolved.

To measure the gas sensing potency of optimum Al/Ga co-doped ZNSs-film sample grown by the sol-gel method, a sensor must be indigenously designed, and the sensing mechanism must be understood. Sample characterisations are necessary to determine the optical, morphological and electrical correlation effects useful for the development devices. A comprehensive understanding of the mechanisms behind the modifications of the overall characteristics of ZnO NSs-film co-doped with Al/Ga is significant. Experimental results must be compared and validated with other similar findings. Thus, high-density AGZO nanofilm with diverse morphology was synthesised and subsequently characterised to evaluate the structural, optical, electrical and gas sensing properties of the NSs-film. However, despite extensive research on ZnO nanostructure synthesis and characterisation, well-controlled ZnO nanostructures-based films with desirable electrical and optical properties are far from being achieved.

To summarise the issues that arise in this process, the sensor fabrication step requires the addition of various dopants which is very complicated and time-consuming. Reproducible and controlled growth of ZnO nanostructures with desirable attributes using an easy method is necessary for many applications. Although several methods have been used to synthesise ZnO nanostructures, they suffer from many

challenges. Vapour solid (VS) and vapour-liquid-solid (VLS) require a high temperature for the nanostructures' growth, while radio frequency (RF) sputtering requires costly instruments and a particular laboratory setup. The sol-gel method is cost-effective and can generate controlled nanostructures of ZnO with morphology and dopants. However, the uses of sol-gel method for synthesising are not well described. One dimensional (1D) and two dimensional (2D) ZnO nanostructures have high surface to volume ratios, which make them valuable for many applications (Ali et al., 2010). Although there are different methods to fabricate 2D ZnO nanostructures, the sol-gel spin coating method is the easiest and is able to fabricate 2D ZnO nanostructures at low temperatures. Based on the above-mentioned issues, this research proposes alternative methods in order to minimize cost and time.

1.3 Research Objectives

Based on the previously mentioned research and the research gaps the following objectives are set:

- i) To synthesise pure, ZnO NSs-thin films doped with Al content from (0 to 5 at.%), and co-doped with Al/Ga with varying Ga level (0-5) at.% by using a combined sol-gel and spin coating technique on Si-substrate by thermal annealing.
- ii) To determine the processing parameters (annealing temperature, time annealing, Ga dopant concentration and laser energy) dependent structure, morphology, optical and electrical properties of synthesised AZO samples through comprehensive characterisations on Si-substrate.
- iii) To measure the hydrogen gas sensitivity of grown AGZO nanofilm (containing vertically aligned nanorods morphology) by manufacturing a gas sensor for the two types of annealing (thermal and laser).

1.4 Scope of the Study

This research involves the synthesis and thorough characterisations of ZnO NSs-thin films doped with Al and co-doped with Al/Ga. Samples will be analysed to determine their structural, morphological, optical and electrical features. The design of a gas sensor using the optimum AGZO film sample is the application-oriented target. The preparation of a series of NSs-thin films of pure zinc-oxide (ZO), Al-doped zinc-oxide (AlZO), and ZnO co-doped with Al/Ga (AGZO) with diverse morphologies on the p-type Si (100) substrates will be carried out using combined sol-gel and spin-coating techniques. Raw materials of zinc-acetate-dehydrate, ZnAc [$\text{Zn}(\text{CH}_3\text{COO})_2 \cdot 2\text{H}_2\text{O}$], aluminium-nitrate-nonahydrate [$\text{Al}(\text{NO}_3)_3 \cdot 9\text{H}_2\text{O}$], gallium nitrate nonahydrate [$\text{Ga}(\text{NO}_3)_3 \cdot 9\text{H}_2\text{O}$], 2-propanol [$\text{C}_3\text{H}_8\text{O}$] and ethanolamine (EA) will be used for growing such ZnO thin films. Zn precursor solution will be prepared by the dissolution of [$\text{Zn}(\text{CH}_3\text{COO})_2 \cdot 2\text{H}_2\text{O}$] in 2-propanol (0.1 M) and EA. Spin-coating at 3000 rpm speed and drying at 300 °C for 20 min on Si wafer will be completed. Furthermore, the execution of thermal and laser annealing treatment on the prepared thin films for the improvement of properties will be carried out. Samples of thermal annealing will be performed at different temperature (425, 450, 475 and 500) °C and for varying time durations (between 0 to 3 h) and for the laser energy annealing to examine their impact of overall properties. Al doping concentration will be fixed at 1 at.% and Ga contents will be varied (0 to 5 at.%) to optimize the composition of AGZO nanofilms.

Room temperature structural and morphological characterisations of the as-grown thin films samples will be taken using atomic force microscopy (AFM), scanning electron microscopy (SEM), field emission scanning electron microscopy (FESEM), X-ray diffraction (XRD) and energy-dispersive X-ray (EDX) spectroscopy. The optical properties of these samples will be examined using photoluminescence (PL), Raman and UV-Vis spectroscopy. The 4-point probe method will be used to measure the electrical resistivity and (I-V) characteristics of samples. Finally, a hydrogen gas sensor will be designed based on the optimum AGZO nanofilm sample to demonstrate its potential for gas sensing. The sensing performance of the synthetic

AGZO NSs film will be evaluated at 100 °C and 150 °C under varying hydrogen gas concentrations of 250, 500, 1250 and 1750 ppm.

1.5 Significance of the Study

Understanding the growth mechanism and improvement of various properties of AGZO nanofilm is fundamentally important. Despite this, a systematic approach for depositing such film with high quality and desired morphology using the sol-gel assisted method has not yet been developed. Thus, this study is significant in terms of developing a systematic method for the synthesis of good quality AGZO films required for diverse applications especially for gas sensors and transparent electrodes. This study is expected to resolve some of the issues related to traditional growth methods. Furthermore, the achieved new findings will contribute towards the development of ZnO-NSs thin films co-doped with Al/Ga which are useful for efficient gas sensors. So far, the effects of substrate, annealing laser shooting, growth time and temperature on the structure, morphology, optical and electrical properties of AGZO films have not been systematically determined. Growth of high quality samples requires careful optimization of the processing parameters.

Controlled morphology and structure with high crystallinity required for the optoelectronic industries are believed to be achievable by sol-gel assisted spin-coating and laser annealing methods. The performance evaluation of the deposited AGZO nanofilms in terms of efficiency, cost, large scale reproducibility and environmental friendliness will be an interesting aspect to investigate. Using the proposed characterisation tools, it is possible to measure the defects, crystallinity, NSs morphology, optical band gap, optical absorbance, elemental traces, NPs shape, size and distribution, surface roughness, crystal density, Hall mobility, resistivity, carrier concentrations and gas sensing attributes. Furthermore, the proposed method can also be extended to grow another kind of semiconductor NSs in a well-controlled and reproducible manner.

1.6 Thesis Outline

This thesis is composed of five chapters with the following highlights:

Chapter 1 provides a brief research background to introduce the problem and to show why this research topic is relevant and worth undertaking. A brief review is provided to show the existing research gap and the issues to be resolved. The problem statement, research objectives, scope of the research and the significance are described.

Chapter 2 presents a detailed literature review to justify the problem statement and the need for further research to fill the current gaps in the literature. A gentle introduction will be presented to the development of ZnO NSs, various methods of synthesis with their notable merits and demerits, characterisation tools, un-doped and doped ZnO films, and applications of these NSs. Detailed theories of ZnO nanostructure growth mechanisms, the principle of the techniques used to grow ZnO films and the mechanisms for gas sensing are discussed.

Chapter 3 describes the research methodology in terms of raw materials, compositions, sample preparation techniques, optimization procedure, characterisation tools and their models, methods of data collection and subsequent analysis.

Chapter 4 discusses the experimental results and analysis, interpreting them using various mechanisms, and comparing the present results with earlier findings in the literature. This chapter demonstrates how the results obtained can fulfil the proposed research objectives. The role of different annealing temperatures, time and laser energy shoots on the surface morphological, structural, electrical and optical behaviours of ZnO-NSs thin films co-doped with Al/Ga synthesised by sol-gel and laser annealing are underlined. Furthermore, the gas sensing attributes of the optimum sample are discussed.

Chapter 5 concludes the thesis by proposing recommendations for future research in this field.

REFERENCES

- Ab Kadir, R. Taib, N.M., Ahmad, W.R.W., Aziz, A.A. and Zoolfakar, A.S. (2018), March 'Effect of substrates on Zinc Oxide thin films fabrication using sol-gel method', In *IOP Conference Series: Materials Science and Engineering*, (340, No. 1), 012002. IOP Publishing.
- Abdulgafour, H.I., Yam, F.K., Hassan, Z., Al-Heuseen, K. and Jawad, M.J. (2011). 'ZnO nanocoral reef grown on porous silicon substrates without catalyst' ,*Journal of Alloys and Compounds*, (509,18), 5627-5630.
- Abrinaei, F. (2019). 'Al dopant-dependent third-order nonlinear optical parameters in ZnO thin films under CW Nd: YAG laser irradiation', *Journal of Materials Science: Materials in Electronics*, (30,9), 8619-8628.
- Adamyanyan, A.Z., Adamyanyan, Z.N., Aroutiounian, V.M., Arakelyan, A.H., Touryan, K.J. and Turner, J.A. (2007) 'Sol-gel derived thin-film semiconductor hydrogen gas sensor', *International Journal of Hydrogen Energy*, (32,16), 4101-4108.
- Aksoy, S., Caglar, Y., Ilıcan, S. and Caglar, M. (2012) 'Sol-gel derived Li-Mg co-doped ZnO films: Preparation and characterization via XRD, XPS, FESEM', *Journal of Alloys and Compounds*, (512,1), 171-178.
- Al Abdullah, K., Awad, S., Zaraket, J. and Salame, C. (2017) 'Synthesis of ZnO Nanopowders By Using Sol-Gel and Studying Their Structural and Electrical Properties at Different Temperature', *Energy Procedia*, (119), 565-570.
- Al Asmar, R., Juillaguet, S., Ramonda, M., Giani, A., Combette, P., Khoury, A. and Foucaran, A. (2005) 'Fabrication and characterization of high quality undoped and Ga₂O₃-doped ZnO thin films by reactive electron beam co-evaporation technique', *Journal of crystal growth*, Vol(275,3-4), 512-520.
- Al-Azawi, A.M., Al-Asedy, H.J., Bidin, N. and Abbs, K.N. (2016) 'ZnO QDs Deposited on Si by Sol-Gel Method: Role of Annealing Temperature on Structural and Optical Properties', *Modern Applied Science*, (10,4), 12.
- Al-Hardan, N H., M J. Abdullah and Aziz, A A.(2010) 'Sensing mechanism of hydrogen gas sensor based on RF-sputtered ZnO thin films' ," *International journal of hydrogen energy* (35).

- Ali, S.M.U., Nur, O., Willander, M. and Danielsson, B. (2010) 'A fast and sensitive potentiometric glucose microsensor based on glucose oxidase coated ZnO nanowires grown on a thin silver wire', *Sensors and Actuators B: Chemical*, (145,2), 869-874.
- Al-Salman, H. S. & Abdullah, M. J. (2013) 'Structural, optical, and electrical properties of Schottky diodes based on undoped and cobalt-doped ZnO nanorods prepared by RF-magnetron sputtering' *Materials Science and Engineering B*, (16,178), 1048-1056.
- Alshemary, A.Z. Goh, Y.F. Shakir, I. and Hussain, R.(2015) 'Synthesis, characterization and optical properties of chromium doped β -Tricalcium phosphate', *Ceramics International*, (41,1), 1663-1669.
- Alsultany, F.H. Hassan, Z. and Ahmed, N.M.(2016) 'Catalyst-free growth of ZnO nanowires on ITO seed layer/glass by thermal evaporation method: effects of ITO seed layer laser annealing temperature', *Superlattices and Microstructures*, (92), 68-79.
- Arif, M., Sanger, A. Vilarinho, P.M. and Singh, A. (2018). 'Effect of annealing temperature on structural and optical properties of sol-gel-derived ZnO thin films', *Journal of Electronic Materials*, (47,7), 3678-3684.
- Arguello, C.A. Rousseau, D.L. and Porto, S.P.D.S. (1969) 'First-order Raman Effect in wurtzite-type crystals', *Physical Review*, (181,3), 1351.
- Arooj, S. Nazir, S. Nadhman, A. Ahmad, N. Muhammad, B. Ahmad, I. and R Abbasi, R. (2015) 'Novel ZnO: Ag nanocomposites induce significant oxidative stress in human fibroblast malignant melanoma (Ht144) cells', *Beilstein journal of nanotechnology* (6).
- Asghar, M. Noor, H. Awan, M.S. Naseem, S. and Hasan, M.A. (2008) 'Post-annealing modification in structural properties of ZnO thin films on p-type Si substrate deposited by evaporation', *Materials Science in Semiconductor Processing*, (11,1), 30-35.
- Atanas, J.P. Al Asmar, R., Khoury, A. and Foucaran, A. (2006) 'Optical and structural characterization of ZnO thin films and fabrication of bulk acoustic wave resonator (BAW) for the realization of gas sensors by stacking ZnO thin layers fabricated by e-beam evaporation and rf magnetron sputtering techniques', *Sensors and Actuators A: Physical*, (127,1), 49-55.

- Avci, N., Smet, P.F., Lauwaert, J., Vrielinck, H. and Poelman, D. (2011) 'Optical and structural properties of aluminium oxide thin films prepared by a non-aqueous sol-gel technique', *Journal of sol-gel science and technology*, (59,2), 327-333.
- Ayana, D G. V Prusakova, C Collini, M V. Nardi, R Tatti, M Bortolotti and L Lunelli. (2016) 'Sol-gel synthesis and characterization of undoped and Al-doped ZnO thin films for memristive application', *AIP Advances* (6).
- Bach, L.G., Nguyen, N.G. and Ho, V.T.T. (2016) 'Enhanced light scattering by preferred orientation control of Ga doped ZnO films prepared through MOCVD', *International Journal of Photoenergy*.
- Balaprakash, V. Gowrisankar, P. Rajkumar, R. and Sudha, S. (2018) 'Preparation and characterization of aluminum doped zinc oxide (AZO) nanorods',. *Sādhanā*, (43,6), 86.
- Bandyopadhyay, S. Paul, G.K. Roy, R. Sen, S.K. and Sen, S. (2002) 'Study of structural and electrical properties of grain-boundary modified ZnO films prepared by sol-gel technique', *Materials Chemistry and Physics*, (74,1), 83-91.
- Bao, D., Gu, H and Kuang, A. (1998) 'Sol-gel-derived c-axis oriented ZnO thin films', *Thin solid films*, (312,1), 37-39.
- Barrett, C.S. and Massalski, T.B.(1980). *Structure of Metals*. 3rd. Pergamon Press Oxford.
- Baruah, S. and Dutta, J., 2009. Hydrothermal growth of ZnO nanostructures. *Science and Technology of Advanced Materials*, (10,1), 013001.
- Baruwati, B.D K. Kumar, D. K., and S V. Manorama. S.V. (2006) 'Hydrothermal synthesis of highly crystalline ZnO nanoparticles: A competitive sensor for LPG and EtOH', *Sensors and Actuators Chemical B*, (119).
- Basyooni, M.A. Shaban, M. and El Sayed, A.M. (2017). 'Enhanced gas sensing properties of spin-coated Na-doped ZnO nanostructured films', *Scientific reports*, (7), 41716.
- Behera, D. and Acharya, B.S. (2008) 'Nano-star formation in Al-doped ZnO thin film deposited by dip-dry method and its characterization using atomic force microscopy, electron probe microscopy, photoluminescence and laser Raman spectroscopy', *Journal of luminescence*,(128,10), 1577-1586.

- Berna, A. (2010) 'Metal oxide sensors for electronic noses and their application to food analysis', *Sensors*, (10,4), 3882-3910.
- Bhattacharyya, P. Basu, P.K. Saha, H. and Basu, S. (2007) 'Fast response methane sensor using nanocrystalline zinc oxide thin films derived by sol-gel method', *Sensors and Actuators B: Chemical*, (124,1), 62-67.
- Bornside, D. C. Macosko, and L.E. Scriven, L. E. (1987) 'On the modeling of spin coating', *Journal of imaging technology*, (13,4), 122-130.
- Bouhssira, N. Abed, S. Tomasella, E. Cellier, J. Mosbah, A. Aida, M.S. and Jacquet, M. (2006) 'Influence of annealing temperature on the properties of ZnO thin films deposited by thermal evaporation', *Applied Surface Science*, (252,15), 5594-5597.
- Boukhicha, R. Charpentier, C. Prod'Homme, P. Cabarrocas, R. Lerat, J. F. Emerald, T. and Johnson, E. (2014) 'Influence of sputtering conditions on the optical and electrical properties of laser-annealed and wet-etched room temperature sputtered ZnO: Al thin films', *Thin Solid Films* (555), 1-17.
- Bright, V.M. Kolesar, E.S. and Hauschild, N.T. (1994) May 'Investigation of the sensitivity, selectivity, and reversibility of the chemically-sensitive field-effect transistor (CHEMFET) to detect NO₂, C₃H₉PO₃ and BF₃', *In Aerospace and Electronics Conference.1994, NAECON, Proceedings of the IEEE National*, 342-349.
- Brillson, L J. and Y Lu. Y. (2011) 'ZnO Schottky barriers and Ohmic contacts', *Journal of Applied Physics*, (109).
- Brungs, M.P. Mauchausse, C. Stroescu, D. and TRIMM, D. (1992). 'The Evaluation of Hydrogen Detectors for Use in Coal-Mines', *Journal of The Institute of Energy*, (65,463), 66-69.
- Brungs, W A. Holderman, T S. and M T. Southerland, M. T. (1992). 'Synopsis of water-effect ratios for heavy metals as derived for site-specific water quality criteria (No." PB-93-157584/XAB). *Environmental Protection Agency* .
- Brus, L. (1986). 'Electronic wave functions in semiconductor clusters: experiment and theory', *The Journal of Physical Chemistry*, (90,12), 2555-2560.
- Bu, I.Y. (2016). 'Sol-gel production of p-type ZnO thin film by using sodium doping', *Superlattices and Microstructures*, (96), 59-66.

- Caglar, M. Caglar, Y. Aksoy, S. and Ilcan, S. (2010). 'Temperature dependence of the optical band gap and electrical conductivity of sol-gel derived undoped and Li-doped ZnO films', *Applied Surface Science*, (256,16), 4966-4971.
- Cai, Y. Li, X. Sun, P. Wang, B. Liu, F. Cheng, P. Du, S. and Lu, G. (2013). 'Ordered ZnO nanorod array film driven by ultrasonic spray pyrolysis and its optical properties', *Materials Letters*, (112), 36-38.
- Calleja, J.M. and Cardona, M. (1977). 'Resonant raman scattering in ZnO', *Physical Review B*, (16,8), 3753.
- Campbell, S.A. (2001). 'The Science and Engineering of Microelectronic Fabrication', *The Oxford Series in Electrical and Computer Engineering*. Oxford university press.
- Carreras, P. Antony, A. Rojas, F. and Bertomeu, J. (2011). 'Electrical and optical properties of Zn-In-Sn-O transparent conducting thin films', *Thin Solid Films*, (520,4), 1223-1227.
- Cavalcante, L.S. Anicete-Santos, M. Pontes, F.M. Souza, I.A. Santos, L.P.S. Rosa, I.L.V. Santos, M.R.M.C. Santos-Júnior, L.S. Leite, E.R. and Longo, E. (2007). 'Effect of annealing time on morphological characteristics of Ba (Zr, Ti) O₃ thin films', *Journal of alloys and compounds*, (437,1-2), 269-273.
- Chandra, A.D. Debdulal, K. Fouran, S. Kumar, A.D. Pellegrini, G. Ramesh, C. and Paolo, M. (2010). 'Synthesis of ZnO Nanostructures Using Different Metal Catalyst: Morphology and Photoluminescence Characteristics', *Journal of nanoscience and nanotechnology*, (10,4), 2933-2937.
- Chang, S.C. (2014). 'Post-annealed gallium and aluminum co-doped zinc oxide films applied in organic photovoltaic devices', *Nanoscale research letters*, 9(1), 562.
- Chaitra, U. Kekuda, D. and Rao, K.M. (2017). 'Effect of annealing temperature on the evolution of structural, microstructural, and optical properties of spin coated ZnO thin films', *Ceramics International*, (43,9), 7115-7122.
- Chatelon, J.P. Terrier, C. Bernstein, E. Berjoan, R. and Roger, J.A. (1994). 'Morphology of SnO₂ thin films obtained by the sol-gel technique', *Thin solid films*, (247,2), 162-168.
- Chen, J.T. Wang, J. Zhuo, R.F. Yan, D. Feng, J.J. Zhang, F. and Yan, P.X. (2009). 'The effect of Al doping on the morphology and optical property of ZnO

- nanostructures prepared by hydrothermal process', *Applied Surface Science*, (255,7), 3959-3964.
- Chen, M.F. Chen, Y. P. Hsiao, W. T. and Gu, Z.P. (2007). 'Laser direct write patterning technique of indium tin oxide film', *Thin Solid Films*, (515,24), 8515-8518.
- Chen, Y. W. Liu, Y. C. Lu, S. X. Xu, C. S. Shao, C. L. et al. (2005). 'Optical properties of ZnO and ZnO: In nanorods assembled by sol-gel method', *The Journal of chemical physics*, (123,13), 134701.
- Chen, Y.W. Liu, Y.C. Lu, S.X. Xu, C.S. Shao, C.L. Wang, C. Zhang, J.Y. Lu, Y.M. Shen, D.Z. and Fan, X.W. (2005). Optical properties of ZnO and ZnO: In nanorods assembled by sol-gel method. *The Journal of chemical physics*, (123,13), p.134701.
- Cheng, H.C. Chen, C.F. Tsay, C.Y. and Leu, J.P. (2009). 'High oriented ZnO films by sol-gel and chemical bath deposition combination method', *Journal of Alloys and Compounds*, (475,1-2), L46-L49.
- Cheng, J P. Liao, Z M. Shi, D. Liu, F. and X B. Zhang, X B.(2009).' Oriented ZnO nanoplates on Al substrate by solution growth technique', *Journal of Alloys and Compounds*, (480).
- Cheng, W. Wu, P. Zou, X. and Xiao, T. (2006). 'Study on synthesis and blue emission mechanism of ZnO tetrapodlike nanostructures', *Journal of applied physics*, (100,5), 054311.
- Choi, K J. and H W. Jang.(2010) 'One-dimensional oxide nanostructures as gas-sensing materials: review and issues'," *Sensors*, (10).
- Choppali, U. (2006). 'Low temperature polymeric precursor derived zinc oxide thin films'(68), 2.
- Costa, B.C. Morilla-Santos, C. and Lisboa-Filho, P.N. (2015). 'Effects of time exposure and low power sonochemical treatment on ZnO mesostructures', *Materials Science in Semiconductor Processing*, (35), 81-89.
- Cruz, M.A. Zarzosa, G.O. Castañón, G.M. and Martinez, J.R. (2012). 'Characterization of ZnO threads obtained using dip coating method at room temperature', *Materials Letters*, (78), 159-161.
- Cui, J. (2008). 'Defect control and its influence on the exciton emission of electrodeposited ZnO nanorods', *The Journal of Physical Chemistry C*, (112,28), 10385-10388.

- Dhingra, M. Singh, N.K. Shrivastava, S. Kumar, P.S. and Annapoorni, S. (2013). 'Worm like zinc oxide nanostructures as efficient LPG sensors', *Sensors and Actuators A: Physical*, (190), 168-175.
- Diaz De Leon, C.L. Olivas-Armendariz, I. Hernandez Paz, J.F. Gomez-Esparza, C.D. Reyes-Blas, H. Hernandez Gonzalez, M. Velasco-Santos, C. Rivera-Armenta, J.L. and Rodriguez-Gonzalez, C.A. (2017). 'Synthesis by Sol-Gel and Cytotoxicity of Zinc Oxide Nanoparticles Using Wasted Alkaline Batteries', *Digest Journal of Nanomaterials and Biostructures*, (12,2), 371-379.
- Dicaire, I. Chin, S. and Thévenaz, L. (2011), June. 'Structural slow light can enhance Beer-Lambert absorption', *In Slow and Fast Light* (p. SLWC2). Optical Society of America.
- Du, X. Li, J. and X. Bi, X. (2017). 'The role of Ga partial substitution for Al in the enhanced conductivity of transparent AZO thin film. *Journal of Alloys and Compounds*, (698), 128-132.
- Duan, Y H. Duan, Y. Chen, P. Tao, Y. Yang, Y Q. and Zhao, Y. (2015). 'High-performance flexible Ag nanowire electrode with low-temperature atomic-layer-deposition fabrication of conductive-bridging ZnO film', *Nanoscale research letters*, (10).
- Dutta, M. Ghosh, T. and Basak, D. (2009). 'N doping and Al-N co-doping in sol-gel ZnO films: Studies of their structural, electrical, optical, and photoconductive properties', *Journal of electronic materials*, (38,11), 2335-2342.
- Ebrahimifard, R. Golobostanfard, M.R. and Abdizadeh, H. (2014). 'Sol-gel derived Al and Ga co-doped ZnO thin films: An optoelectronic study', *Applied Surface Science*, (290), 252-259.
- Eichhorn, M., *Laser physics: from principles to practical work in the lab*. 2014: Springer Science & Business Media.
- El Hichou, A. Addou, M. Ebothe, J. and Troyon, M. (2005). 'Influence of deposition temperature (Ts), air flow rate (f) and precursors on cathodoluminescence properties of ZnO thin films prepared by spray pyrolysis', *Journal of luminescence*, (113,3-4), 183-190.

- El-Yadouni, A. Boudrioua, A. Loulergue, J.C. Sallet, V. and Triboulet, R. (2005). 'Growth and optical characterization of ZnO thin films deposited on sapphire substrate by MOCVD technique', *Optical Materials*, (27,8), 1391-1395.
- Emslie, A.G. Bonner, F.T. and Peck, L.G. (1958). 'Flow of a viscous liquid on a rotating disk', *Journal of Applied Physics*, (29,5), 858-862.
- Ergin, B. Ketenci, E. and Atay, F. (2009). 'Characterization of ZnO films obtained by ultrasonic spray pyrolysis technique', *international journal of hydrogen energy*, (34,12), 5249-5254.
- Etcheverry, L P. Flores W H. and E C. Moreira, E C. (2018). 'Annealing effects on the structural and optical properties of ZnO nanostructures', *Materials Research*, (21).
- Fan, H. Knez, M. Scholz, R., Nielsch, K. Pippel, E. Hesse, D. Gösele, U. and Zacharias, M. (2006). 'Single-crystalline MgAl₂O₄ spinel nanotubes using a reactive and removable MgO nanowire template', *Nanotechnology*, (17,20), 5157.
- Fang, M. and Liu, Z.W. (2017). 'Controllable size and photoluminescence of ZnO nanorod arrays on Si substrate prepared by microwave-assisted hydrothermal method', *Ceramics International*, (43,9), 6955-6962.
- Farooqi, M.M.H. and Srivastava, R.K. (2019). 'Effect of Annealing Temperature on Structural, Photoluminescence and Photoconductivity Properties of ZnO Thin Film Deposited on Glass Substrate by Sol-Gel Spin Coating Method', *Proceedings of the National Academy of Sciences, India Section A: Physical Sciences*, 1-15.
- Farrag, A.A.G. and Balboul, M.R. (2017). 'Nano ZnO thin films synthesis by sol-gel spin coating method as a transparent layer for solar cell applications', *Journal of Sol-Gel Science and Technology*, (82,1), 269-279.
- Fedel, M. (2009) *Environmentally friendly hybrid coatings for corrosion protection: silane based pre-treatments and nanostructured waterborne coatings*, PhD Thesis, University of Trento, Trento.
- Feynman, R.P. (1960). 'There's plenty of room at the bottom', *Engineering and science*, (23,5), 22-36.
- Flack, W.W. Soong, D.S. Bell, A.T. and Hess, D.W. (1984). 'A mathematical model for spin coating of polymer resists', *Journal of Applied Physics*, (56,4), 1199-1206.

- Flemban, T.H. (2017) *High Quality Zinc Oxide Thin films and Nanostructures Prepared by Pulsed Laser Deposition for Photodetectors*, Doctoral dissertation.
- Galceran Mestres, M. (2010) Synthesis and characterization of optical nanocrystals and nanostructures. An approach to transparent laser nanoceramics. (Doctoral dissertation, Universitat Rovira i Virgili).
- Geng, Y. Guo, L. Xu, S.S. Sun, Q.Q. Ding, S.J. Lu, H.L. and Zhang, D.W. (2011). 'Influence of Al doping on the properties of ZnO thin films grown by atomic layer deposition', *The Journal of Physical Chemistry C*, (115,25), 12317-12321.
- Ghosh, R. Basak, D. and Fujihara, S. (2004). 'Effect of substrate-induced strain on the structural, electrical, and optical properties of polycrystalline ZnO thin films', *Journal of Applied Physics*, (96,5), 2689-2692.
- Gondal, M.A. Drmosh, Q.A. Yamani, Z.H. and Saleh, T.A. (2009). 'Synthesis of ZnO₂ nanoparticles by laser ablation in liquid and their annealing transformation into ZnO nanoparticles', *Applied surface science*, (256,1), 298-304.
- Gorman, B. and Anderson, H. (2004). 'Processing and characterization of yttrium-stabilized zirconia thin films on polyimide from aqueous polymeric precursors', *Thin solid films*, (457,2), 258-263.
- Goswami, N. and D K. Sharma. (2010). 'Structural and optical properties of unannealed and annealed ZnO nanoparticles prepared by a chemical precipitation technique', *Physica E: Low-dimensional Systems and Nanostructures*, (42).
- Grabowska, J. Nanda, K.K. McGlynn, E. Mosnier, J.P. and Henry, M.O. (2005). 'Studying the growth conditions, the alignment and structure of ZnO nanorods', *Surface and Coatings Technology*, (200,1-4), 1093-1096.
- Greene, L.E. Law, M. Goldberger, J. Kim, F. Johnson, J.C. Zhang, Y. Saykally, R.J. and Yang, P. (2003). 'Low-temperature wafer-scale production of ZnO nanowire arrays', *Angewandte Chemie*, (115,26), 3139-3142.
- Han, N. Tian, Y. Wu X. and Chen, Y.(2009). 'Improving humidity selectivity in formaldehyde gas sensing by a two-sensor array made of Ga-doped ZnO', *Sensors and Actuators B: Chemical*, (138).
- Henni, A. Merrouche, A. Telli, L. and Karar, A. (2016). 'Studies on the structural, morphological, optical and electrical properties of Al-doped ZnO nanorods

- prepared by electrochemical deposition', *Journal of Electroanalytical Chemistry*, (763), 149-154.
- Hong, N.H. Sakai, J. and Brizé, V. (2007). 'Observation of ferromagnetism at room temperature in ZnO thin films', *Journal of Physics: Condensed Matter*, (19,3), 036219.
- Hooker, S A. (2002)). Nanotechnology advantages applied to gas sensor development. *In The nanoparticles 2002 conference proceedings*. October (1-7). Business Communications Co. (n.d.).
- Hosono, H. and D C. Paine, D C. (2010) *Handbook of transparent conductors*. n.p.
- Hou, Y. Soleimanpour, A.M. and Jayatissa, A.H. (2013). 'Low resistive aluminum doped nanocrystalline zinc oxide for reducing gas sensor application via sol-gel process', *Sensors and Actuators B: Chemical*, (177), 761-769.
- Hou, Y. and Jayatissa, A.H. (2017). 'Influence of laser doping on nanocrystalline ZnO thin films gas sensors', *Progress in Natural Science: Materials International*, (27,4), 435-442.
- Houng, B. Hsi, C.S. Hou, B.Y. and Fu, S.L. (2008). 'Fabrication and properties evaluation of aluminum and ruthenium co-doped zinc oxide thin films', *Journal of Alloys and Compounds*, (456,1-2), 64-71.
- Hsiao, W T. Tseng, S F. Chung, C K. Chiang, D. Huang, K C. Lin, K M. and M F. Chen, M F.(2015). 'Effect on structural, optical and electrical properties of aluminum-doped zinc oxide films using diode laser annealing', *Optics & Laser Technology*, (68), 41-47.
- Hsiao, W.T. Tseng, S.F. Huang, K.C. and Chiang, D. (2013). 'Electrode patterning and annealing processes of aluminum-doped zinc oxide thin films using a UV laser system', *Optics and Lasers in Engineering*, (51,1), 15-22.
- <http://www.indosawedu.com/four-probe-resistivity-measurement.php>.
- <https://www2.chemistry.msu.edu/faculty/reusch/VirtTxtJml/Spectrpy/UV-Vis/uvspec>.
- Hu, X. Masuda, Y. Ohji, T. and Kato, K. (2008). 'Synthesis of highly conductive and transparent ZnO nanowhisker films using aqueous solution', *Journal of the ceramic society of japan*, (116,1351),384-388.
- Huang, H.C. and T.E. Hsieh, (2010). 'Highly stable precursor solution containing ZnO nanoparticles for the preparation of ZnO thin film transistors', *Nanotechnology*, (21,29). 295707.

- Huang, L.J. Li, B.J. and Ren, N.F. (2016). 'Enhancing optical and electrical properties of Al-doped ZnO coated polyethylene terephthalate substrates by laser annealing using overlap rate controlling strategy', *Ceramics International*, (42).
- Huang, M.H. Mao, S. Feick, H. Yan, H. Wu, Y. Kind, H. Weber, E. Russo, R. and Yang, P. (2001). 'Room-temperature ultraviolet nanowire nanolasers. *science*, (292,5523), 1897-1899.
- Hübert, T. Boon-Brett, L. Black G and Banach. U. (2011). 'Hydrogen sensors—a review." *Sensors and Actuators B: Chemical*, (157),329-352.
- Ilican, S. Caglar, Y. Caglar, M. and Demirci, B. (2008). 'Polycrystalline indium-doped ZnO thin films: preparation and characterization', *J. Optoelectron. Adv. Mater*, (10), 2592-2598.
- Irimpan, L. Krishnan, B. Deepthy, A. Nampoori, V.P.N. and Radhakrishnan, P. (2007). 'Excitation wavelength dependent fluorescence behaviour of nano colloids of ZnO', *Journal of Physics D: Applied Physics*, (40,18), 5670.
- Islam, M.R. Rahman, M. and Podder, J. (2019). 'Structural, optical and photocatalysis properties of sol–gel deposited Al-doped ZnO thin films', *Surfaces and Interfaces*, (16), 120-126.
- Isshiki, M. Sichanugrist, P. Abe, Y. Oyama, T. Odaka, H. and Konagai, M. (2014). 'New method to measure whole-wavelength transmittance of TCO substrates for thin-film silicon solar cells', *Current Applied Physics*, (14,12), 1813-1818.
- Ivanova, T. Harizanova, A. Koutzarova, T. and Vertruyen, B. (2015). 'Optical characterization of sol–gel ZnO: Al thin films', *Superlattices and Microstructures*, (85), 101-111.
- Jagadish, C. and S.J. Pearton, (2011) *Zinc oxide bulk, thin films and nanostructures: processing, properties, and applications*: Elsevier.
- Jayathilake, D.S. Peiris, T.N. Sagu, J.S., Potter, D.B. Wijayantha, K.U. Carmalt, C.J. and Southee, D.J. (2017). Microwave assisted synthesis and processing of Al, Ga and Al, Ga Co-doped ZnO for the pursuit of optimal conductivity for transparent conducting film fabrication. *ACS Sustain. Chem. Eng.*
- Janotti, A. and Van de Walle, C.G. (2007). Native point defects in ZnO. *Physical Review B*, (76,16), 165202.
- Jimenez-Cadena, G. Comini, E. Ferroni, M. Vomiero, A. and Sberveglieri, G. (2010). 'Synthesis of different ZnO nanostructures by modified PVD process and

- potential use for dye-sensitized solar cells', *Materials Chemistry and Physics*, (124,1), 694-698
- Jimenez-Gonzalez, A.E. Urueta, J.A.S. and Suarez-Parra, R. (1998). 'Optical and electrical characteristics of aluminum-doped ZnO thin films prepared by solgel technique', *Journal of Crystal Growth*, (192,3-4), 430-438.
- Jin, Z.C. Hamberg, I. and Granqvist, C.G. (1988). 'Optical properties of sputter-deposited ZnO: Al thin films', *Journal of applied physics*, (64,10), 5117-5131.
- Johnson, E.V. Prod'homme, P. Boniface, C. Huet, K. Emeraud, T. and i Cabarrocas, P.R., (2011). 'Excimer laser annealing and chemical texturing of ZnO: Al sputtered at room temperature for photovoltaic applications', *Solar Energy Materials and solar cells*, (95,10), 2823-2830.
- Johnson, J.C. Yan, H. Yang, P. and Saykally, R.J.(2003). 'Optical cavity effects in ZnO nanowire lasers and waveguides', *The journal of physical chemistry B*, (107,34), 8816-8828.
- Joseph, B. Gopchandran, K.G. Manoj, P.K. Koshy, P. and Vaidyan, V.K. (1999). 'Optical and electrical properties of zinc oxide films prepared by spray pyrolysis', *Bulletin of Materials Science*, (22,5), 921-926.
- Kamalasanan, M. and Chandra, S. (1996). 'Sol-gel synthesis of ZnO thin films', *Thin Solid Films*, (288,1),112-115.
- Kang, D.W. Kim, S.J. Moon, T.H. Lee, H.M. and Han, M.K. (2010). 'Effect of Ga doping on transparent and conductive Al-doped ZnO films prepared using magnetron cosputtering', *Japanese Journal of Applied Physics*, (49,12R), 125801.
- Kao, M., H. Chen, and Young, S. (2010). 'Effects of preannealing temperature of ZnO thin films on the performance of dye-sensitized solar cells', *Applied Physics A*, (98,3), 595-599.
- Kara, K. Tüzemen, E.Ş. and Esen, R. (2014). 'Annealing effects of ZnO thin films on p-Si (100) substrate deposited by PFCVAD', *Turkish Journal of Physics*, (38,2), 238-244.
- Keskenler, E. Turgut, G. and Doğan, S. (2012). 'Investigation of structural and optical properties of ZnO films co-doped with fluorine and indium', *Superlattices and Microstructures*, (52,1), 107-115.

- Khan, R. Uthirakumar, P. Bae, K.B. Leem, S.J. and Lee, I.H. (2016). 'Localized surface plasmon enhanced photoluminescence of ZnO nanosheets by Au nanoparticles', *Materials Letters*, (163), 8-11.
- Khan, I.M. Chattha, M.S., Khan, Z.M. and Mateen, A. (2018). Optimization of Thin Film Thicknesses in Tandem Solar Cells. *Journal of Nanoelectronics and Optoelectronics*, (13,1), 104-110.
- Kim, H. J. Jeon, J. A. Choi, J. Y. Kim, J. Hong, J. T. Seo, H. Lee, D. G. Lee, K. J. and Son, M. K. (2009). 'Proposal of optimal process parameters for polymethylmethacryl plastic adhesion using a pulsed Nd: YAG laser', *Optical Engineering*. (48,8), 084301.
- Kim, D.K. and Kim, H.B. (2016). Effect of post-annealing time on the properties of sputtered Al-doped ZnO thin films. *Journal of Materials Science: Materials in Electronics*, (27,11), 11366-11370.
- Kim, H. Pique, A. Horwitz, J.S. Murata, H. Kafafi, Z.H. Gilmore, C.M. and Chrisey, D.B. (2000). 'Effect of aluminum doping on zinc oxide thin films grown by pulsed laser deposition for organic light-emitting devices', *Thin solid films*, (377), 798-802.
- Kim, J., Sekiya, T., Miyokawa, N., Watanabe, N., Kimoto, K., Ide, K., Toda, Y., Ueda, S., Ohashi, N., Hiramatsu, H. and Hosono, H., 2017. Conversion of an ultra-wide bandgap amorphous oxide insulator to a semiconductor. *NPG Asia Materials*, 9(3), p.e359.
- Kim, J.P. Bae, J.S. Hong, T.E. Won, M.S. Yoon, J.H. Lee, B.S. and Lee, H.J. (2010). 'Optical and electrical properties of ZnO films, codoped with Al and Ga deposited at room temperature by an RF sputtering method', *Thin Solid Films*, (518,22), 6179-6183.
- Kim, K.K. Niki, S. Oh, J.Y. Song, J.O. Seong, T.Y. Park, S.J. Fujita, S. and Kim, S.W. (2005). 'High electron concentration and mobility in Al-doped n-ZnO epilayer achieved via dopant activation using rapid-thermal annealing.
- Kirby, S. and Van Dover, R. (2009). 'Improved conductivity of ZnO through co-doping with In and Al', *Thin Solid Films*, (517,6), 1958-1960.
- Klimov, V.I. Mikhailovsky, A.A. Xu, S. Malko, A. Hollingsworth, J.A. Leatherdale, C.A. Eisler, H.J. and Bawendi, M.G. (2000). 'Optical gain and stimulated emission in nanocrystal quantum dots', *Science*, (290,5490), 314-317.

- Kohan, A.F. Ceder, G. Morgan, D. and Van de Walle, C.G. (2000). 'First-principles study of native point defects in ZnO', *Physical Review B*, (61,22), 15019.
- Kohl, D. (1989). 'Surface processes in the detection of reducing gases with SnO₂-based devices', *Sensors and actuators*, (18).
- Koidis, C. Logothetidis, S. Kassavetis, S. Laskarakis, A. Hastas, N.A. and Valassiades, O. (2010). 'Growth mechanisms and thickness effect on the properties of Al-doped ZnO thin films grown on polymeric substrates', *physica status solidi (a)*, (207,7), 1581-1585.
- Kolmakov, A. Zhang, Y. Cheng, G. and M Moskovits, M. (2003). 'Detection of CO and O₂ using tin oxide nanowire sensors', *Advanced materials*, (15).
- Kumar, M. and Kumar, D. (2010). 'The deposition of nanocrystalline TiO₂ thin film on silicon using Sol-Gel technique and its characterization', *Microelectronic Engineering*, (87).
- Kumar, N S., K V. Bangera and G K. Shivakumar. "Effect of annealing on the properties of zinc oxide nanofiber thin films grown by spray pyrolysis technique." *Applied Nanoscience* 4 (2014).
- Kumar, R. Kumar G. and Umar, A. (2014). 'Pulse laser deposited nanostructured ZnO thin films: A review', *Journal of nanoscience and nanotechnology*, (14,2), 1911-1930.
- Kumar, V. Kumar, V. Som, S. Yousif, A. Singh, N. O M. Ntwaeaborwa O M. and H Swart. H C.(2014). Effect of annealing on the structural, morphological and photoluminescence properties of ZnO thin films prepared by spin coating', *Journal of colloid and interface science*, (428), 8-15.
- Kumar, V. Singh, R.G. Singh, N., Kapoor, A. Mehra, R.M. and Purohit, L.P. (2013). 'Synthesis and characterization of aluminum-boron co-doped ZnO nanostructures', *Materials Research Bulletin*, (48,2), 362-366.
- Lawrence, C.J. and Zhou, W. (1991). 'Spin coating of non-Newtonian fluids', *Journal of non-newtonian fluid mechanics*, (39,2), 137-187.
- Lee, D. (2012). *ZnO Nanostructure Synthesis & Laser Direct Writing Process for Optoelectronic Devices*. Doctoral dissertation, UC Berkeley.
- Lee, J H. Chou, C Y. Bi, Z. C F. Tsai, C F. and Wang, H.(2009). 'Growth-controlled surface roughness in Al-doped ZnO as transparent conducting oxide', *Nanotechnology*, (20).

- Lee, J.H. and Park, B.O. (2003). 'Transparent conducting ZnO: Al, In and Sn thin films deposited by the sol-gel method', *Thin Solid Films*, (426,1-2), 94-99.
- Lee, W. and Leem, J.Y. (2018). 'Enhancement of the Ultraviolet Photoresponsivity of Al-doped ZnO Thin Films Prepared by using the Sol-gel Spin-coating Method', *Journal of the Korean Physical Society*, (72,5), 610-614.
- Lee, W. Shin, S. Jung, D.R. Kim, J. Nahm, C., Moon, T. and Park, B. (2012). 'Investigation of electronic and optical properties in Al- Ga codoped ZnO thin films', *Current Applied Physics*, (12,3), 628-631.
- Lei, Z. LIAN, J.S. Liu, Y.H. and Jiang, Q. (2008). 'Influence of preparation methods on photoluminescence properties of ZnO films on quartz glass', *Transactions of Nonferrous Metals Society of China*, (18,1), 145-149.
- Li, C. Furuta, M. Matsuda, T. Hiramatsu, T. Furuta, H. and Hirao, T. (2009). 'Effects of substrate on the structural, electrical and optical properties of Al-doped ZnO films prepared by radio frequency magnetron sputtering', *Thin Solid Films*, (517,11), 3265-3268.
- Lian, L. and Sottos, N.R. (2004). 'Stress effects in sol-gel derived ferroelectric thin films', *Journal of Applied Physics*, (95,2), 629-634.
- Lieber, C M. and Z L. Wang. (2007). 'Functional nanowires', *MRS bulletin*, (32), 99-108 .
- Liu, D. Lv, Y. Zhang, M. Liu, Y., Zhu, Y. Zong, R. and Zhu, Y. (2014). 'Defect-related photoluminescence and photocatalytic properties of porous ZnO nanosheets', *Journal of Materials Chemistry A*, (2,37), 15377-15388.
- Liu, H. Avrutin, V., Izyumskaya, N. Özgür, Ü. & Morkoç, H. (2010). 'Transparent conducting oxides for electrode applications in light emitting and absorbing devices', *Superlattices and Microstructures*, (48,5), 458-484.
- Liu, K. Sakurai, M and Aono, M. (2010). 'ZnO-based ultraviolet photodetectors', *Sensors*, (10,9), 8604-8634.
- Liu, M. (2010) *Synthesis of ZnO nanowires and applications as gas sensors*. PhD, Thesis. University of Saskatchewan.
- Look, D.C. (2001). Recent advances in ZnO materials and devices. *Materials Science and Engineering: B*, (80,1-3), 383-387.
- Luo, J.T. Quan, A.J. Zheng, Z.H. Liang, G.X. Li, F. Zhong, A.H. Ma, H.L. Zhang, X.H. and Fan, P. (2018). 'Study on the growth of Al-doped ZnO thin films with

- (1120) and (0002) preferential orientations and their thermoelectric characteristics', *RSC Advances*, (8,11), 6063-6068.
- Lupan, O. Ursaki, V V. Chai, G Chow, L Emelchenko, G A. Tiginyanu I M. and Redkin, A N. (2010). 'Selective hydrogen gas nanosensor using individual ZnO nanowire with fast response at room temperature', *Sensors and Actuators B: Chemical*, (144).
- Lupan, O. Chai, G. and Chow, L. (2008). 'Novel hydrogen gas sensor based on single ZnO nanorod', *Microelectronic Engineering*, (85,11), 2220-2225.
- Lupan, O. Chow, L. Shishiyanu, S. Monaico, E. Shishiyanu, T. Şontea, V. Cuenya, B.R. Naitabdi, A. Park, S. and Schulte, A. (2009). 'Nanostructured zinc oxide films synthesized by successive chemical solution deposition for gas sensor applications', *Materials Research Bulletin*, (44,1), 63-69.
- Maache, M. Devers, T. and Chala, A. (2017). 'Al-doped and pure ZnO thin films elaborated by sol-gel spin coating process for optoelectronic applications', *Semiconductors*, (51,12), 1604-1610.
- Mahadik, M A. Shinde, S S. Hunge, Y M. Mohite, V S. Kumbhar, S S. Moholkar A V. and Bhosale C H. (2014). 'UV assisted photoelectrocatalytic oxidation of phthalic acid using spray deposited Al doped zinc oxide thin films', *Journal of Alloys and Compounds*, (611) , 446-451.
- Major, S. Banerjee, A. and Chopra, K. (1985). 'Optical and electronic properties of zinc oxide films prepared by spray pyrolysis', *Thin Solid Films*, (125,1), 179-185
- Makhlouf, H. Karam, C. Lamouchi, A. Tingry, S. Miele, P. Habchi, R. Chtourou, R. and Bechelany, M. (2018). 'Analysis of ultraviolet photo-response of ZnO nanostructures prepared by electrodeposition and atomic layer deposition', *Applied Surface Science*, (444), 253-259.
- Makino, T. Chia, C.H. Tuan, N.T. Segawa, Y. Kawasaki, M. Ohtomo, A. Tamura, K. and Koinuma, H. (2000). 'Radiative and nonradiative recombination processes in lattice-matched (Cd, Zn) O/(Mg, Zn) O multiquantum wells', *Applied Physics Letters*, (77,11), 1632-1634.
- Makuku, O. Mbaiwa, F. and Sathiaraj, T.S. (2016). 'Structural, optical and electrical properties of low temperature grown undoped and (Al, Ga) co-doped ZnO thin films by spray pyrolysis', *Ceramics International*, (42,13), 14581-14586.

- Maldonado, F. and A. Stashans, (2010). ‘Al-doped ZnO: Electronic, electrical and structural properties’, *Journal of Physics and Chemistry of Solids*, (71,5), 784-787.
- Maller, R. (2016). ‘Defects and dopants in zinc oxide: a study of the optoelectronic properties of thin films prepared by spray pyrolysis.
- Mamat, M.H. Malek, M.F. Hafizah, N.N. Khusaimi, Z. Musa, M.Z. and Rusop, M. (2014). ‘Fabrication of an ultraviolet photoconductive sensor using novel nanostructured, nanohole-enhanced, aligned aluminium-doped zinc oxide nanorod arrays at low immersion times’, *Sensors and Actuators B: Chemical*, (195), 609-622.
- Mamat, M.H. Sahdan, M.Z. Amizam, S. Rafaie, H.A. Khusaimi, Z. and Rusop, M. (2009). ‘Optical and electrical properties of aluminum doped zinc oxide thin films at various doping concentrations’, *Journal of the Ceramic Society of Japan*, (117,1371), 1263-1267.
- Mamat, M.H. Sahdan, M.Z. Khusaimi, Z. Ahmed, A.Z. Abdullah, S. and Rusop, M. (2010). ‘Influence of doping concentrations on the aluminum doped zinc oxide thin films properties for ultraviolet photoconductive sensor applications’, *Optical Materials*, (32,6), 696-699.
- Mandal, S. Goswami, M.L.N. Das, K. Dhar, A. and Ray, S.K. (2008). ‘Temperature dependent photoluminescence characteristics of nanocrystalline ZnO films grown by sol–gel technique’, *Thin Solid Films*, (516,23), 8702-8706.
- Mansoori, G.A. (2005) *Principles of nanotechnology: molecular-based study of condensed matter in small systems*. World Scientific.
- McKenna, K. and Shluger, A. (2009). ‘The interaction of oxygen vacancies with grain boundaries in monoclinic HfO₂’, *Applied Physics Letters*, (95).
- Meyerhofer, D. (1978). ‘Characteristics of resist films produced by spinning’, *Journal of Applied Physics*, (4,(7), 3993-3997.
- Michael, K.Ã. and Fritzsche, W. (2008) *Nanotechnology: an introduction to nanostructuring techniques*. John Wiley & Sons.
- Middleman, S. (1998) *An introduction to fluid dynamics: principles of analysis and design*. New York: Wiley.
- Min, Y. Tuller, H.L. Palzer, S. Wöllenstein, J. and Böttner, H. (2003). ‘Gas response of reactively sputtered ZnO films on Si-based micro-array’, *Sensors and Actuators B: Chemical*, (93,1-3),435-441.

- Mitra, P. Chatterjee, A.P. and Maiti, H.S. (1998). 'ZnO thin film sensor', *Materials Letters*, (35,1-2), 33-38.
- Mohammad, S.M. Hassan, Z. Talib, R.A. Ahmed, N.M. Al-Azawi, M.A. Abd-Alghafour, N.M. Chin, C.W. and Al-Hardan, N.H. (2016). 'Fabrication of a highly flexible low-cost H₂ gas sensor using ZnO nanorods grown on an ultra-thin nylon substrate', *Journal of Materials Science: Materials in Electronics*, (27,9), 9461-9469.
- Moharram, A.H. Mansour, S.A. Hussein, M.A. and Rashad, M. (2014). 'Direct precipitation and characterization of ZnO nanoparticles', *Journal of Nanomaterials*, 20
- Moon, M.R. An, C.H. Na, S. Jeon, H. Jung, D. Kim, H. and Lee, H.J. (2012). 'Effects of Post Annealing on the Electrical Properties of ZnO Thin Films Transistors', *Applied Microscopy*, (42,4), 212-217.
- Moormann, H. D Kohl, D. and G Heiland, D. (1979), 'Work function and band bending on clean cleaved zinc oxide surfaces', *Surface Science*, (1979).
- Motlan, Siregar, N. and Panggabean, J. (2020) . The effect of post annealing time on structural and optical properties of ZnO thin films by sol-gel spin coating method. In *Journal of Physics: Conference Series*.(2020, January).IOP Publishing.
- Moseley, P.T. (1997). 'Solid state gas sensors', *Measurement Science and technology*, (8,3), 223.
- Muchuweni, E., Sathiaraj, T.S. and Nyakoty, H., 2016. Effect of gallium doping on the structural, optical and electrical properties of zinc oxide thin films prepared by spray pyrolysis. *Ceramics International*, 42(8), pp.10066-10070.
- Muhsien, M.A. and Hamdan, H.H. (2012). Preparation and characterization of p-Ag₂O/n-Si heterojunction devices produced by rapid thermal oxidation', *Energy Procedia*, (18), 300-311.
- Munawaroh, H. Wahyuningsih, S. and A H. Ramelan, A H. (2017). 'Synthesis and Characterization of Al doped ZnO (AZO) by Sol-gel Method', *In IOP Conference Series: Materials Science and Engineering* (2017, February).
- Murali, K.R. and Thirumoorthy, P. (2010). 'Characteristics of sol-gel deposited alumina films', *Journal of Alloys and Compounds*, (500,1), 93-95.

- Musat, V. Teixeira, B. Fortunato, E. Monteiro, R.C.C. and Vilarinho, P. (2004). 'Al-doped ZnO thin films by sol-gel method', *Surface and Coatings Technology*, (180), 659-662.
- Muthukumar, S. Gorla, C.R. Emanetoglu, N.W. Liang, S. and Lu, Y. (2001). 'Control of morphology and orientation of ZnO thin films grown on SiO₂/Si substrates. *Journal of Crystal Growth*, 225(2-4), pp.197-201.
- Nagase, T., Ooie, T. and Sakakibara, J., 1999. A novel approach to prepare zinc oxide films: excimer laser irradiation of sol-gel derived precursor films', *Thin Solid Films*, (357,2), 151-158.
- Ng, H T. Chen, B Li, J. Han, J. Meyyappan, M. Wu, J and E E. Haller, E. E. (2003) 'Optical properties of single-crystalline ZnO nanowires on m-sapphire', *Applied Physics Letters*, (82).
- Ngom, B.D. Mpahane, T. Manyala, N. Nemraoui, O. Buttner, U. Kana, J.B. Fasasi, A.Y. Maaza, M. and Beye, A.C. (2009). 'Structural and optical properties of nano-structured tungsten-doped ZnO thin films grown by pulsed laser deposition', *Applied Surface Science*, (255,7), 4153-4158.
- Nian, Q. M Y. Zhang, M Y. Schwartz B D. and G J. Cheng, G. J. (2014). 'Ultraviolet laser crystallized ZnO: Al films on sapphire with high Hall mobility for simultaneous enhancement of conductivity and transparency', *Applied Physics Letters*, (104).
- Nicolescu, M. Anastasescu, M., Preda, S. Calderon-Moreno, J.M. Osiceanu, P. Gartner, M. Teodorescu, V.S. Kampylafka, A.V.V. Aperathitis, E. and Modreanu, M. (2010). 'Investigation of microstructural properties of nitrogen doped ZnO thin films formed by magnetron sputtering on silicon substrate', *Journal of Optoelectronics and Advanced Materials*, (12,5), 1045.
- Oh, B.Y. Jeong, M.C. Kim, D.S. Lee, W. and Myoung, J.M. (2005). 'Post-annealing of Al-doped ZnO films in hydrogen atmosphere', *Journal of Crystal Growth*, (281,2-4), 475-480.
- Ohyama, M. Kouzuka, H and Yoko, T. (1997). 'Sol-gel preparation of ZnO films with extremely preferred orientation along (002) plane from zinc acetate solution. *Thin solid films*, (306,1), 78-85.
- Omar, O. Ray, A.K. Hassan, A.K. and Davis, F. (1997). 'Resorcinol calixarenes (resorcarenes): Langmuir-Blodgett films and optical properties', *Supramolecular Science*, (4,3-4), 417-421.

- Omata, T. Takahashi, K. Hashimoto, S. Maeda, Y. Nose K. and S. Otsuka-Yao-Matsuo, S. (2009). 'Synthesis of Zinc Oxide Nanocrystals Showing Size Dependent UV Emission. in Meeting Abstracts', *The Electrochemical Society*, 129.
- Özer, N. Cronin, J.P. Yao, Y.J. and Tomsia, A.P. (1999). 'Optical properties of sol-gel deposited Al₂O₃ films. *Solar energy materials and solar cells*, (59,4), 355-366.
- Özgür, Ü. Alivov, Y.I. Liu, C. Teke, A. Reshchikov, M. Doğan, S., Avrutin, V.C.S.J. Cho, S.J. and Morkoc, H. (2005). 'A comprehensive review of ZnO materials and devices', *Journal of applied physics*, (98,4), 11.
- Pan, C.J. Tu, C.W. Tun, C.J. Lee, C.C. and Chi, G.C. (2007). 'Structural and optical properties of ZnO epilayers grown by plasma-assisted molecular beam epitaxy on GaN/sapphire (0001)', *Journal of crystal growth*, (305,1), 133-136.
- Pan, J. Chen, J. Huang, Q. Khan, Q., Liu, X. Tao, Z. Zhang, Z. Lei, W. and Nathan, A. (2016). 'Size tunable ZnO nanoparticles to enhance electron injection in solution processed QLEDs', *ACS Photonics*, (3,2), 215-222.
- Pan, Z. Tian, X. Wu, S. Yu, X. Li, Z. Deng, J. Xiao, C. Hu, G. and Wei, Z. (2013). 'Investigation of structural, optical and electronic properties in Al-Sn co-doped ZnO thin films.
- Pant, B. Park, M. Kim, H Y. and Park, S J. (2016). 'Ag-ZnO photocatalyst anchored on carbon nanofibers: synthesis, characterization, and photocatalytic activities', *Synthetic Metals*.
- Park, K.C. Ma, D.Y. and Kim, K.H. (1997). 'The physical properties of Al-doped zinc oxide films prepared by RF magnetron sputtering', *Thin Solid Films*, (305,1-2), 201-209.
- Park, M. and Han, S M. (2015). 'Enhancement in conductivity through Ga, Al dual doping of ZnO nanofibers. *Thin Solid Films*, (590). 307-310.
- Park, W I. Kim, J S. Yi, G C. Bae, M H. and H J. Lee, H J. (2004). 'Fabrication and electrical characteristics of high-performance ZnO nanorod field-effect transistors,' *Applied Physics Letters*, (85).
- Park, W.I. Kim, D.H. Jung, S.W. and Yi, G.C. (2002). 'Metalorganic vapor-phase epitaxial growth of vertically well-aligned ZnO nanorods', *Applied Physics Letters*, (80,22), 4232-4234.

- Patterson, A.L. (1939). 'The Scherrer formula for X-ray particle size determination', *Physical review*, (56,10), 978.
- Poole Jr, C.P. and Owens, F.J. (2003). '*Introduction to nanotechnology*. John Wiley & Sons.
- Prasad, S. Walck, S. and Zabinski, J. (2000). 'Microstructural evolution in lubricious ZnO films grown by pulsed laser deposition', *Thin Solid Films*, (360,1), 107-117.
- Pu, Y K. Guo, Z G. Kang, Z D. J Ma, J. Guan, Z C. Zhang G Y. and E G. Wang. E G.(2002). 'Comparative characterization of high-density plasma reactors using emission spectroscopy from VUV to NIR', *Pure and applied chemistry*, (74).
- Ramamoorthy, K. Sanjeeviraja, C. Jayachandran, M. Sankaranarayanan, K. Misra, P. and Kukreja, L.M. (2006). 'Development of a novel high optical quality ZnO thin films by PLD for III–V opto-electronic devices', *Current Applied Physics*, (6,1), 103-108.
- Ragazzon, M.R. (2018) *Parameter Estimation in Atomic Force Microscopy: Nanomechanical Properties and High-speed Demodulation*. Doctoral thesis.
- Reddy, B.S. Reddy, S.V. and Reddy, N.K. (2013). 'Physical and magnetic properties of (Co, Ag) doped ZnO nanoparticles. *Journal of Materials Science: Materials in Electronics*, (24,12), 5204-5210.
- Reynolds, D.C., Look, D.C. and Jogai, B. (1996). 'Optically pumped ultraviolet lasing from ZnO', *Solid State Communications*, (99,12), 873-875.
- Ri, K.H. Wang, Y. Zhou, W.L. Gao, J.X. Wang, X.J. and Yu, J. (2011). 'The structural properties of Al doped ZnO films depending on the thickness and their effect on the electrical properties', *Applied Surface Science*, (258,4), 1283-1289.
- Ri, K.H. Wang, Y.B. Zhou, W.L. Gao, J.X. Wang, X.J. and Yu, J. (2011). 'The effect of SiO₂ buffer layer on the electrical and structural properties of Al-doped ZnO films deposited on soda lime glasses', *Applied Surface Science*, (257,13), 5471-5475.
- Riedel, W. Tang, Y. Ohm, W. Chen, J. M C. Lux-Steiner M C. and Gledhill, S. (2015). 'Effect of initial galvanic nucleation on morphological and optical properties of ZnO nanorod arrays', *Thin Solid Films*, (574), 177-183.
- Ronning, C. Gao, P.X. Ding, Y. Wang, Z.L. and Schwen, D. (2004). 'Manganese-doped ZnO nanobelts for spintronics', *Applied physics letters*, (84,5), 783-785.

- Rout, C S. Krishna, S H. and A Govindaraj, A. (2006). 'Hydrogen and ethanol sensors based on ZnO nanorods, nanowires and nanotubes', *Chemical Physics Letters*, (418),11.
- Sabeeh, S H. and R H. Jassam. (2018). 'The effect of annealing temperature and Al dopant on characterization of ZnO thin films prepared by sol-gel method', *Results in Physics*, (10), (212-216).
- Sahu, N. Parija, B. and Panigrahi, S. (2009). 'Fundamental understanding and modeling of spin coating process: A review', *Indian Journal of Physics*, (83,4), 493-502.
- Salam, S. Islam, M. and Akram, A. (2013). 'Sol-gel synthesis of intrinsic and aluminum-doped zinc oxide thin films as transparent conducting oxides for thin film solar cells', *Thin Solid Films*, (529), 242-247.
- Samavati, A. Mustafa, M. Othaman Z. and Ghoshal, S. (2015). 'Ge nanoislands grown by radio frequency magnetron sputtering: comprehensive investigation of surface morphology and optical properties', *Journal of Nanomaterials*, (16,1), 101.
- Sanchez-Juarez, A. Tiburcio-Silver, A. and Ortiz, A. (1998). 'Properties of fluorine-doped ZnO deposited onto glass by spray pyrolysis', *Solar energy materials and solar cells*, (52,3-4), 301-311.
- Saravanakumar, B., Mohan, R., Thiyagarajan, K. and Kim, S.J., 2013. Investigation of UV photoresponse property of Al, N co-doped ZnO film. *Journal of Alloys and Compounds*, 580, pp.538-543.
- Sarjidan, M.A. Salleh, N.S. Basri, S.H. Razali R., Za'aba, N.K. and Majid, W.H. (2014). 'Tunable optoelectronic properties of sol-gel derived ZnO nanostructure thin film by annealing treatment', *Materials Express*, (4,5), 422-428.
- Saw, K.G. Ibrahim, K. Lim, Y.T. and Chai, M.K. (2007). 'Self-compensation in ZnO thin films: An insight from X-ray photoelectron spectroscopy, Raman spectroscopy and time-of-flight secondary ion mass spectroscopy analyses', *Thin Solid Films*, (515,5), 2879-2884.
- Scharnagl, K. Eriksson, M. Karthigeyan, A. Burgmair, M. Zimmer, M. and Eisele, I. (2001). 'Hydrogen detection at high concentrations with stabilised palladium', *Sensors and Actuators B: Chemical*, (78,1-3), 138-143.

- Schmidt-Mende, L and MacManus-Driscoll J L.(2007). ‘ZnO–nanostructures, defects, and devices’, *Materials today*, (10).
- Schütz, C. Kalmbach, C. Fu, R. Witzendorff, P and Overmeyer, L. (2014). ‘Nir-cw-laser annealing of room temperature sputtered zno: Al’, *Physics Procedia*, (55), 1073-1082.
- Schwandt, C. and Fray, D.J. (2000). ‘Hydrogen sensing in molten aluminium using a commercial electrochemical sensor’, *Ionics*, (6,3-4), 222-229.
- Scorticati, D. Illiberi, A. Bor T C. and Eijt, S W.(2015). ‘Thermal annealing using ultra-short laser pulses to improve the electrical properties of Al: ZnO thin films’, *Acta materialia*, (98), 327-335.
- Seiyama, T. Kato, A. Fujiishi, K. and M Nagatani, M. (1962). ‘A new detector for gaseous components using semiconductive thin films’, *Analytical Chemistry*, (34,11), 1502-1503.
- Sennaroglu, A. (2006) *Solid-state lasers and applications*. CRC press.
- Serier, H. Gaudon, M. and Ménétrier, M. (2009). ‘Al-doped ZnO powdered materials: Al solubility limit and IR absorption properties’, *Solid State Sciences*, (11,7), 1192-1197.
- Serrano, J. Romero, A.H. Manjon, F.J. Lauck, R. Cardona, M. and Rubio, A. (2004). ‘Pressure dependence of the lattice dynamics of ZnO: An ab initio approach’, *Physical Review B*, (69,9), 094306.
- Serrao, F.J. Sandeep, K.M. Bhat, S. and Dharmaprakash, S.M. (2016), Sol-gel derived Al-Ga co-doped transparent conducting oxide ZnO thin films. *In AIP Conference Proceedings* (2016, May). AIP Publishing.
- Shahzad, M.B. Qi, Y. Lu, H. and Wang, X. (2013). ‘A study on the Al doping behavior with sol aging time and its effect on structural and optical properties of sol–gel prepared ZnO thin films’, *Thin solid films*, (534), 242-248.
- Shariffudin, S.S., Ibrahim, N.T.C., Sarah, M.S.P. and Hashim, H., 2016, August. Effect of annealing temperature on characteristics of ZnO/CuO nanocomposite thin films. *In Semiconductor Electronics (ICSE), 2016 IEEE International Conference on* (pp. 177-180). IEEE.
- Shastri, V.P. Altankov, G. and Lendlein, A. eds. (2010). ‘Advances in Regenerative Medicine: Role of Nanotechnology, and Engineering Principles. Springer.

- Shi, Q. Zhou, K. Dai, M. Lin, S. Hou, H. Wei, C. and Hu, F. (2014). 'Growth of high-quality Ga–F codoped ZnO thin films by mid-frequency sputtering', *Ceramics International*, (401),211-216.
- Shimizu, Y. Kuwano, N., Hyodo, T. and Egashira, M.(2002). 'High H₂ sensing performance of anodically oxidized TiO₂ film contacted with Pd', *Sensors and Actuators B: Chemical*, (83,1-3), 195-201.
- Shinde, S.S., Shinde, P.S., Bhosale, C.H. and Rajpure, K.Y., 2008. Optoelectronic properties of sprayed transparent and conducting indium doped zinc oxide thin films. *Journal of Physics D: Applied Physics*, 41(10), p.105109.
- Shinde, V.R. Gujar, T.P. Lokhande, C.D. Mane, R.S. and Han, S.H. (2006). 'Mn doped and undoped ZnO films: A comparative structural, optical and electrical properties study', *Materials Chemistry and Physics*, (96,2-3), 326-330.
- Shinde, V.R. Lokhande, C.D. Mane, R.S. and Han, S.H. (2005). 'Hydrophobic and textured ZnO films deposited by chemical bath deposition: annealing effect', *Applied Surface Science*, (245,1-4), 407-413.
- Shu-Wen, X. (2012). 'A study of annealing time effects on the properties of Al: ZnO', *Physics Procedia*, (25), 45-349.
- Siddheswaran, R. Mangalaraja, R.V. Gómez, M.E. Avila, R.E. and Jeyanthi, C.E. (2013). 'Room temperature ferromagnetism in combustion synthesized nanocrystalline Co, Al co-doped ZnO', *Journal of Alloys and Compounds*, (581), 146-149.
- Singh, A. Kumar, S. Das, R. and Sahoo, P K. (2015). 'Defect-assisted saturable absorption characteristics in Mn doped ZnO nano-rods', *Rsc Advances*, (5,108), 88767-88772.
- Song, X. Wang, Z. Liu, Y. Wang, C. and Li, L. (2009). 'A highly sensitive ethanol sensor based on mesoporous ZnO–SnO₂ nanofibers', *Nanotechnology*, (20,7), 075501.
- Sripianem, W. Chuchuyay, A. Kiatthanabumrung, P. Saengow, N. Wichean, T N. Jongthammanurak, S. and Techapiesancharoenkij, R. (2018). 'Effect of aluminium doping concentration on microstructures, optical and electrical properties of ZnO thin films by spray pyrolysis technique', *Materials Today: Proceedings*, (5,3), 9519-9524..

- Studenikin, S.A. Golego, N. and Cocivera, M. (1998). 'Fabrication of green and orange photoluminescent, undoped ZnO films using spray pyrolysis', *Journal of Applied physics*, (84,4), 2287-2294.
- Sukee, A. Kantarak, E. and Singjai, P. (2017) Preparation of Aluminum doped Zinc Oxide Thin Films on Glass Substrate by Sparking Process and Their Optical and Electrical Properties. *In Journal of Physics: Conference Series*. (2017, September). IOP Publishing.
- Sun, X. and Kwok, H S. (1999). 'Optical properties of epitaxially grown zinc oxide films on sapphire by pulsed laser deposition. *Journal of applied physics*, (86,1), 408-411.
- Sun, Y F. Liu, S B. Meng, F L. Liu, J Y. Jin, Z. Kong, L T. and Liu, J H . (2012). 'Metal oxide nanostructures and their gas sensing properties: a review', *Sensors*. (12,3), 2610-2631.
- Taabouche, A. Bouafia, M. Benazzouz, C. Kerdja, T. Bouachiba, Y. Menakh, S. Hanini, F. Kermiche, F. Bouabellou, A. and Amara, S. (2013). 'Effect of Substrates on the Properties of ZnO Thin Films Grown by Pulsed Laser Deposition', *Advances in Materials Physics and Chemistry*, (3), 209-213.
- Takai-Yamashita, C. Ishino, T. Fuji, M. and Inoue, K. (2016). 'Preparation and formation mechanism of ZnO supported hollow SiO₂ nanoparticle by an interfacial reaction through micropores', *Colloids and Surfaces A: Physicochemical and Engineering Aspects*,(493), 9-17.
- Tang, Z.K. Wong, G.K. Yu, P. Kawasaki, M. Ohtomo, A., Koinuma, H. and Segawa, Y. (1998). 'Room-temperature ultraviolet laser emission from self-assembled ZnO microcrystallite thin films', *Applied Physics Letters*, (72,25), 3270-3272.
- Thirunavukkarasu, K. and Jothiramalingam, R. (2013). 'Synthesis and structural characterization of Ga-ZnO nanodisk/nanorods formation by polymer assisted hydrothermal process', *Powder technology*, (239), 308-313.
- Triboulet, R. and Perrière, J. (2003). 'Epitaxial growth of ZnO films', *Progress in Crystal Growth and Characterization of Materials*, (47,2-3), 65-138.
- Tsang, W.M. Wong, F.L. Fung, M.K. Chang, J.C. Lee, C.S. and Lee, S.T. (2008). 'Transparent conducting aluminum-doped zinc oxide thin film prepared by sol-gel process followed by laser irradiation treatment', *Thin Solid Films*, (517,2), 891-895.

- Tsay, C.Y. and Wang, M.C. (2013). 'Structural and optical studies on sol-gel derived ZnO thin films by excimer laser annealing', *Ceramics International*, (39,1), 469-474.
- Tseng, Y.K., Gao, G.J. and Chien, S.C., 2010. Synthesis of c-axis preferred orientation ZnO: Al transparent conductive thin films using a novel solvent method. *Thin Solid Films*, 518(22), pp.6259-6263.
- Tyona, M D. (2013). 'A theoretical study on spin coating technique', *Advances in materials Research*, (2,4), 195.
- Uikey, P. and Vishwakarma, K. (2016). 'Review of zinc oxide (ZnO) nanoparticles applications and properties', *International Journal of Emerging Technology in Computer Science & Electronics*, (21,2), 239-42.
- Vajargah, P.H. Abdizadeh, H. Ebrahimifard, R. and Golobostanfard, M.R. (2013). 'Sol-gel derived ZnO thin films: effect of amino-additives', *Applied Surface Science*, (285), 732-743.
- Van Heerden, J. and Swanepoel, R. (1997). 'XRD analysis of ZnO thin films prepared by spray pyrolysis. *Thin Solid Films*, (299,1), 72-77.
- Vanheusden, K. Warren, W.L. Seager, C.H. Tallant, D.R. Voigt, J.A. and Gnade, B.E. (1996). 'Mechanisms behind green photoluminescence in ZnO phosphor powders', *Journal of Applied Physics*, (79,10), 7983-7990.
- Vimalkumar, T. Poornima, N. K. Jinesh, K. Kartha C. S. and Vijayakumar, K. (2011). On single doping and co-doping of spray pyrolysed ZnO films: Structural, electrical and optical characterisation. *Applied Surface Science*, (257,20), 8334-8340.
- Viswanatha, R. Santra, P.K. Dasgupta, C. and Sarma, D.D. (2007). 'Growth mechanism of nanocrystals in solution: ZnO, a case study', *Physical review letters*, (98,25), 255501.
- Wakelin, J.H. Virgin, H.S. and Crystal, E. (1959). 'Development and comparison of two X-ray methods for determining the crystallinity of cotton cellulose', *Journal of Applied physics*, (30,11), 1654-1662.
- Wang, H. and Akid, R. (2007). 'A room temperature cured sol-gel anticorrosion pre-treatment for Al 2024-T3 alloys', *Corrosion science*, (49,12), 4491-4503.
- Wang, J. Meng, L. Qi, Y. Li, M. Shi, G. and Liu, M. (2009). 'The Al-doping contents dependence of the crystal growth and energy band structure in Al: ZnO thin films', *Journal of Crystal Growth*, (311,8), 2305-2308.

- Wang, N. Yang, Y. and Yang, G. (2011). 'Great blue-shift of luminescence of ZnO nanoparticle array constructed from ZnO quantum dots', *Nanoscale research letters*, (6,1), 338.
- Wang, T. Liu, Y. Fang, Q. Wu, M. Sun, X. and Lu, F. (2011). 'Low temperature synthesis wide optical band gap Al and (Al, Na) co-doped ZnO thin films', *Applied Surface Science*, (257,6), 2341-2345.
- Wang, W. Li, C. Zhang, J. and Diao, X. (2010). 'Effects of atomic oxygen treatment on structures, morphologies and electrical properties of ZnO: Al films', *Applied Surface Science*, (256,14), 4527-4532.
- Wang, X.J. Dong, B. and Lei, M.K. (2006). 'Infrared absorption spectra of Er³⁺-doped Al₂O₃ nanopowders by the sol-gel method', *Journal of sol-gel science and technology*, (39,3), 307-311.
- Wei, P. Zhu, D., Huang, S. Zhou, W. and Luo, F. (2013). 'Effects of the annealing temperature and atmosphere on the microstructures and dielectric properties of ZnO/Al₂O₃ composite coatings', *Applied Surface Science*, (285), 577-582.
- Wei, X.Q. Man, B.Y. Liu, M. Xue, C.S. Zhuang, H.Z. and Yang, C. (2007). 'Blue luminescent centers and microstructural evaluation by XPS and Raman in ZnO thin films annealed in vacuum, N₂ and O₂', *Physica B: Condensed Matter*, (388,1-2), 145-152.
- Weppner, W. 'Solid-state electrochemical gas sensors', *Sensors and Actuators*, (12,2), 107-119.
- Widanarto, W. Senft, C. Senftleben, O. Hansch, W. and Eisele, I. (2011). 'Characterization and sensing properties of ZnO film in FG-FET sensor system for NO₂ detection', *International Journal of Basic & Applied Sciences IJBAS-IJENS*, (11,1), 104-108.
- Wilson, M. Kannangara, K. Smith, G. Simmons, M. and Raguse, B. (2002). 'Nanotechnology: basic science and emerging technologies', Chapman and Hall / CRC Press.
- Wu, J.J. and Liu, S.C., (2002). 'Catalyst-free growth and characterization of ZnO nanorods. *The Journal of Physical Chemistry B*', (106,37), 9546-9551.
- Xu, L. Li, X. Chen, Y. and Xu, F. (2011). Structural and optical properties of ZnO thin films prepared by sol-gel method with different thickness', *Applied Surface Science*, (257,9), 4031-4037.

- Xu, L. Zheng, G. Lai, M. and Pei, S. (2014). 'Annealing impact on the structural and photoluminescence properties of ZnO thin films on Ag substrates', *Journal of Alloys and Compounds*, (583), 560-565.
- Xu, Q. R Hong, D. Huang, H L. Zhang, Z F. Zhang, M K. X P. Chen, X P. and Z Y. Wu, Z Y. 'Laser annealing effect on optical and electrical properties of Al doped ZnO films', *Optics & Laser Technology*, (45), 513-517.
- Yadav, A B. A Pandey, B A. and Jit, S. (2014). 'Effects of Annealing Temperature on the Structural, Optical, and Electrical Properties of ZnO Thin Films Grown on n-Si (100) Substrates by the Sol-Gel Spin Coating Method', *Acta Metallurgica Sinica (English Letters)*, (27,4), 682-688.
- Yadav, A.B. Periasamy, C. and Jit, S. (2015). 'Study of post annealing effects on structural and optical properties of sol-gel derived ZnO thin films grown on n-Si substrate. In *IOP Conference Series: Materials Science and Engineering* (Vol. 73, No. 1, p. 012060). IOP Publishing.
- Yakuphanoglu, F., Ilican, S., Caglar, M. and Caglar, Y., 2007. The determination of the optical band and optical constants of non-crystalline and crystalline ZnO thin films deposited by spray pyrolysis', *Journal of optoelectronics and advanced materials*, (9,7), 2180.
- Yamamoto, T. and Katayama-Yoshida, H. (2001). 'Physics and control of valence states in ZnO by co-doping method', *Physica B: Condensed Matter*, (302), 155-162.
- Yamazoe, N. (1991). 'New approaches for improving semiconductor gas sensors', *Sensors and Actuators B: Chemical*, (5, 1-4), 7-19.
- Yamazoe, N. Fuchigami, J. Kishikawa, M. and Seiyama, T. (1979). 'Interactions of tin oxide surface with O₂, H₂O and H₂', *Surface Science*, (86), 335-344.
- Yan, C. and Xue, D. (2008). 'Solution growth of nano-to microscopic ZnO on Zn', *Journal of Crystal Growth*, (310,7-9), 1836-1840.
- Yan, Y. Zhou, P. Zhang, S.X. Guo, X.G. and Guo, D.M. (2018). 'Effect of substrate curvature on thickness distribution of polydimethylsiloxane thin film in spin coating process', *Chinese Physics B*, (27,6), 068104.
- Yang, Z. Shi, Y.Y. Sun, X.L. Cao, H.T. Lu, H.M. and Liu, X.D. (2010). 'The competition growth of ZnO microrods and nanorods in chemical bath deposition process', *Materials Research Bulletin*, (45,4), 474-480.

- Yilmaz, S. (2014). 'Study of Influence of Annealing Time on Some Physical Properties of ZnO: Cu Nanorods Grown by a Simple Chemical Bath Deposition Method', *Journal of Superconductivity and Novel Magnetism*, (27,4), 1083-1089.
- Yonkoski, R.K. and Soane, D.S. (1992). 'Model for spin coating in microelectronic applications', *Journal of applied physics*, (72,2), 725-740.
- Yoo, J. Lee, J. Kim, S. Yoon, K. Park, I.J. Dhungel, S.K. Karunagaran, B. Mangalaraj, D. and Yi, J. (2005). 'High transmittance and low resistive ZnO: Al films for thin film solar cells', *Thin Solid Films*, (480), 213-217.
- Yousif, M.E. (2014). 'Electromagnetic Radiation Energy and Planck's Constant', *International Journal of Innovative Research in Advanced Engineering (IJIRAE)*, (1,10), .2349-2163.
- Zeng, H. Duan, G. Li, Y. Yang, S. Xu, X. and Cai, W. (2010). 'Blue Luminescence of ZnO nanoparticles based on non-equilibrium processes: defect origins and emission controls', *Advanced Functional Materials*, (20,4), 561-572.
- Zeng, J.N. Low, J. K. Ren, Z. M. Liew, T. and Y.F. Lu, Y.F. (2002). 'Effect of deposition conditions on optical and electrical properties of ZnO films prepared by pulsed laser deposition', *Applied surface science*, (197), 362-367.
- Zerdali, M. Hamzaoui, S. Teherani, F.H. and Rogers, D. (2006). 'Growth of ZnO thin film on SiO₂/Si substrate by pulsed laser deposition and study of their physical properties', *Materials Letters*, (60,4), 504-508.
- Zhang, J. and Que, W. 'Preparation and characterization of sol-gel Al-doped ZnO thin films and ZnO nanowire arrays grown on Al-doped ZnO seed layer by hydrothermal method', *Solar energy materials and solar cells*, (94,12), 2181-2186.
- Zhang, L. Zhao, J. Lu, H. Gong, L., Li, L. Zheng, J. Li, H. and Zhu, Z. (2011). 'High sensitive and selective formaldehyde sensors based on nanoparticle-assembled ZnO micro-octahedrons synthesized by homogeneous precipitation method', *Sensors and Actuators B: Chemical*, (160,1), 364-370.
- Zhang, M Y. and Cheng, G J. (2011) 'Highly conductive and transparent alumina-doped ZnO films processed by direct pulsed laser recrystallization at room temperature', *Applied Physics Letters*, (99,5), 051904.
- Zhang, P. (2008). 'Design And Fabrication Of Chemiresistor Type micro/nano Hydrogen Gas Sensors Using interdigitated Electrodes'.

- Zhang, S B.(2002). ‘The microscopic origin of the doping limits in semiconductors and wide-gap materials and recent developments in overcoming these limits: a review’, *Journal of Physics: Condensed Matter*, (14,34), R881.
- Zhang, S B. Wei, S H. and Zunger, A. (1999). ‘Overcoming doping bottlenecks in semiconductors and wide-gap materials’, *Physica B: Condensed Matter*.
- Zhang, S.B. Wei, S.H. and Zunger, A. (1998). ‘A phenomenological model for systematization and prediction of doping limits in II–VI and I–III–VI compounds’, *Journal of Applied Physics*, (83,6), 3192-3196.
- Zhang, Y. Lin, B. Fu, Z., Liu, C. and Han, W. (2006). ‘Strong ultraviolet emission and rectifying behavior of nanocrystalline ZnO films’, *Optical Materials*, (28,10), 1192-1196.
- Zhang, Z. Bao, C. Yao, W., Ma, S. Zhang, L. and Hou, S. (2011). ‘Influence of deposition temperature on the crystallinity of Al-doped ZnO thin films at glass substrates prepared by RF magnetron sputtering method’, *Superlattices and Microstructures*, (49,6), 644-653.
- Zhao, M. H., Wang, Z. L. and S.X. Mao, S. X. (2004). ‘Piezoelectric characterization of individual zinc oxide nanobelt probed by piezoresponse force microscope’, *Nano Letters*, (4,4), 587-590.
- Zheng, J.H. Jiang, Q. and Lian, J.S. (2011). ‘Synthesis and optical properties of flower-like ZnO nanorods by thermal evaporation method’, *Applied Surface Science*, (257,11), 5083-5087.
- Zhong, W.W. Liu, F. M Cai, L.G. Zhou, C.C. Ding, P. and Zhang, H. (2010). ‘Annealing effects of co-doping with Al and Sb on structure and optical–electrical properties of the ZnO thin films’, *Journal of Alloys and Compounds*, (499,2), 265-268.
- Zhou, H.M. Yi, D.Q. Yu, Z.M. Xiao, L.R. and Li, J. (2007). ‘Preparation of aluminum doped zinc oxide films and the study of their microstructure, electrical and optical properties’, *Thin solid films*, (515,17), 6909-6914.
- Zhu, G. (2017). ‘Investigation of the Mode Structures of Multiphoton Induced Ultraviolet Laser in a ZnO Microrod’, *Journal of Nanotechnology*, .
- Zou, C.W. Yan, X.D. Han, J. Chen, R.Q. Gao, W. and Metson, J. (2009). ‘Study of a nitrogen-doped ZnO film with synchrotron radiation’, *Applied Physics Letters*, (94,17), 171903.

- Zou, J., Zhou, S., Xia, C., Zhang, X., Su, F., Peng, G., Li, X. and Xu, J., 2006. Optical properties of ZnO thin film on γ -LiAlO₂ substrate grown by pulsed laser deposition. *Thin Solid Films*, 496(2), pp.205-207.
- Zu, P. Tang, Z.K. Wong, G.K., Kawasaki, M. Ohtomo, A. Koinuma, H. and Segawa, Y. (1997). 'Ultraviolet spontaneous and stimulated emissions from ZnO microcrystallite thin films at room temperature', *Solid State Communications*, (103,8), 459-463.

APPENDIX A

LIST OF PUBLICATIONS

Journal with Impact Factor

1. **Hayder J. Al-Asedy**, Noriah Bidin, Khaldoon N. Abbas, Mohammed A. Al-Azawia. Structure, morphology and photoluminescence attributes of Al/Ga co-doped ZnO nanofilms: Role of annealing time. *Materials Research Bulletin* 97 (2018) 71–80. <https://doi.org/10.1016/j.materresbull.2017.08.050>. **(Q2,IF: 2.873)**
2. **Hayder J. Al-Asedy**, Ali A. Ati, Noriah Bidin, Siew-Ling Lee. Gallium contents-dependent improved behavior of sol–gel-grown Al:Ga co-doped ZnO nanostructures. *Appl. Phys. A* (2017) 123:665. <https://doi.org/10.1007/s00339-017-1271-0> . **(Q2,IF: 1.604)**
3. **Hayder J. Al-Asedy** ,Al-Khafaji, S.A., Bakhtiar, H. and Bidin, N., 2018. Properties of Al-and Ga-doped thin zinc oxide films treated with UV laser radiation. *Applied Physics A*, 124(3), p.223. <https://doi.org/10.1007/s00339-018-1619-0>. **(Q2,IF:1.604)**
4. **Hayder J. Al-Asedy**, H.J., Bidin, N., Al-khafaji, S.A. and Bakhtiar, H., 2018. Sol-gel grown aluminum/gallium co-doped ZnO nanostructures: Hydrogen gas sensing attributes. *Materials Science in Semiconductor Processing*, 77, pp.50-57. <https://doi.org/10.1016/j.mssp.2018.01.011>. **(Q2,IF:2.593)**
5. Khaldoon N. Abbas, Noriah Bidin, Raad S. Sabry, **Hayder J. Al-Asedy**, Mohammed A. Al-Azawi and Shumaila Islam b. Structures and Emission Features of High-Density ZnO Micro/Nanostructure Grown by an Easy Hydrothermal Method. *Materials Chemistry and Physics*, 2016. 182: 298-307. <https://doi.org/10.1016/j.matchemphys.2016.07.035>. **(Q2,IF:2.210)**

Indexed Scopus Journal

1. **Hayder J. Al-Asedy**, Noriah Bidin, Khaldoon N. Abbas and Mohammed A. Al-Azawi. ZnO QDs Deposited on Si by Sol-Gel Method: Role of Annealing Temperature on Structural and Optical Properties. *Modern Applied Science*, 2016. 10(4): 12. DOI:10.5539/mas.v10n4p12. (**Indexed by SCOPUS**)

Indexed Conference Proceedings

1. Khaldoon N. Abbas, Noriah Bidin, Mohammed A. Al-Azawia and **Hayder J. Al-Asedy**. Nanostructural and Optical Properties of Hierarchical ZnO Grown via Hydrothermal Method. *Jurnal Teknologi*, 2016. 78(3): 1-5. (**Indexed by SCOPUS**)
2. Khaldoon N. Abbas, Noriah Bidin, Mohammed A. Al-Azawia and **Hayder J. Al-Asedy**. Facile Hydrothermal Synthesis of Flower-like ZnO Nanorods without Catalysts. *Jurnal Teknologi*, 2015. 74(8): 15-18. (**Indexed by SCOPUS**)
3. Mohammed A. Al-Azawi, Noriah Bidin, M Abdullah, Abdulrahman K. Ali, Khaleel I. Hassoon, Khaldoon N. Abbas and **Hayder J Al-Asedy**. Surface Plasmon Resonance Effects of Gold Colloids on Optical Properties of N719 Dye in Ethanol. *Optoelectron. Adv. Mater*, 2015. 17(3-4): 264-269. (**Indexed by SCOPUS**)
4. Mohammed A Al-Azawi, Noriah Bidin, M Bououdina, Khaldoon N. Abbas, **Hayder J Al-Asedy**, Omar H Ahmed and Asad A Thahe. The Effect of the Ambient Liquid Medium on the Ablation Efficiency, Size and Stability of Silver Nanoparticles Prepared by Pulse Laser Ablation in Liquid Technique. *Jurnal Teknologi*, 2016. 78(3): 7-11. (**Indexed by SCOPUS**)